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Developments in Microwave photonics

Integrated Microwave Photonics based on hybrid combination of Si_3N_4 -based-TriPleX and InP PICs

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(online)

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- LioniX International is a leading global provider of customized microsystem solutions, in particular integrated photonics-based, in scalable production volumes

Why

- Applying disruptive technologies to solve major societal challenges



**Integrated Photonics is
one of the key enablers**



Scalable Production Volumes

The Gallery,
LioniX Int office and lab



The Gallery,
Cleanroom, PIC production



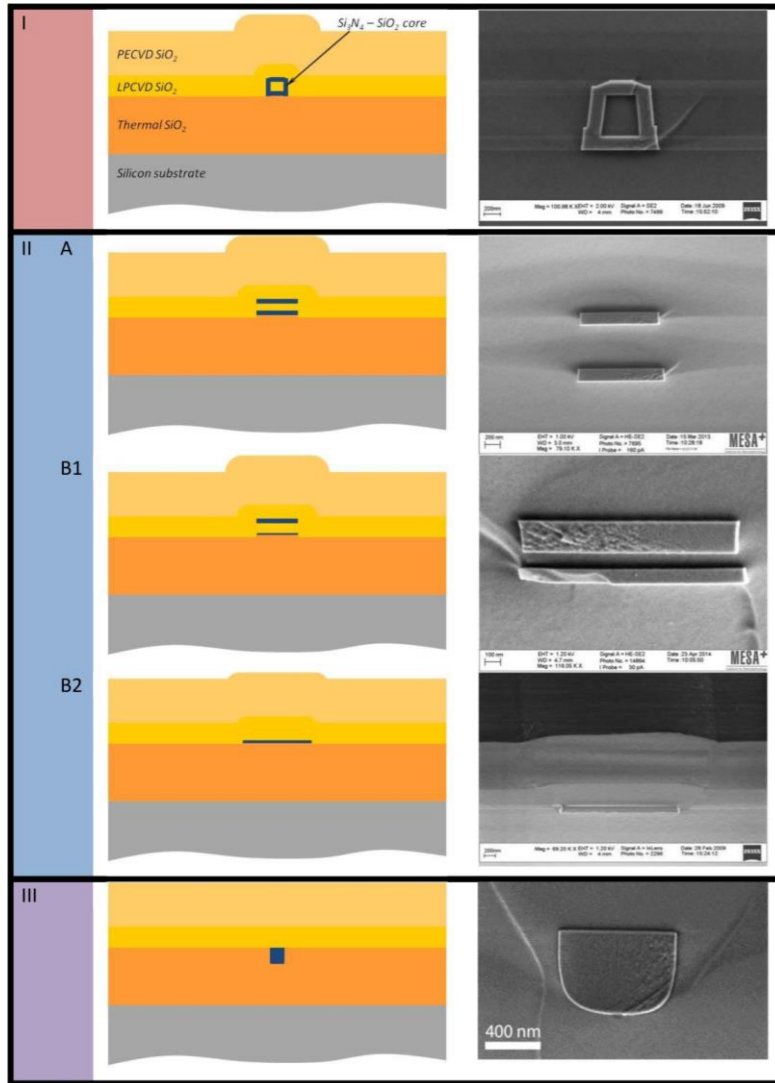
High Tech Factory,
PHIX assembling & packaging Fab



Magic Micro and KANC
Cleanroom, PIC production

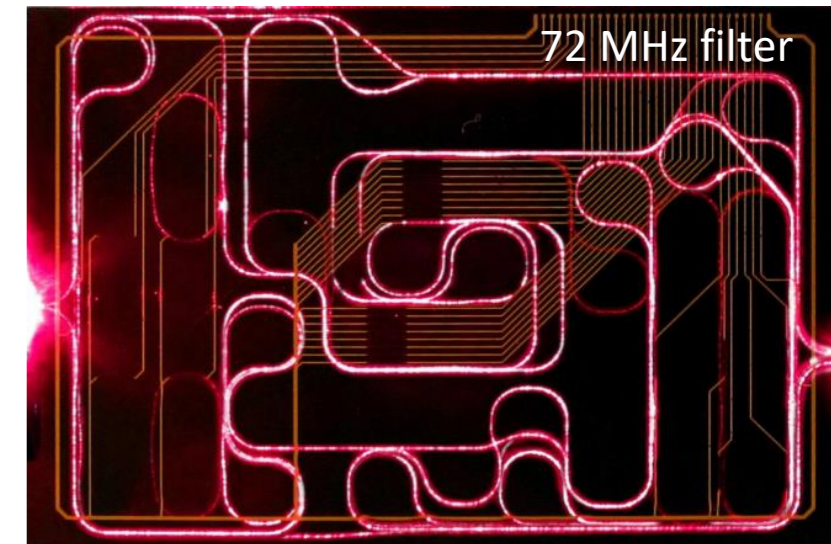


TriPleX™: Some Geometries...



- Core Si_3N_4 and Cladding SiO_2
- High optical powers (watts)
- Low optical attenuation
 - 0.1 dB/cm high confinement
 - 0.001 dB/cm for low confinement
- Adjustable polarization properties
- Broad band (405nm-2350nm)
- Small footprint ($R_{\text{bend}} < 80 \mu\text{m}$)
- Spot-size converters
 - Low coupling loss to SMF (<0.5 dB)
 - Low chip-to-chip coupling loss (< 1 dB)
- Silicon and glass compatible

C. Taddei et al., "High-selectivity on-chip optical bandpass filter with sub-100-MHz flat-top and under-2 shape factor," IEEE PTL, 2019

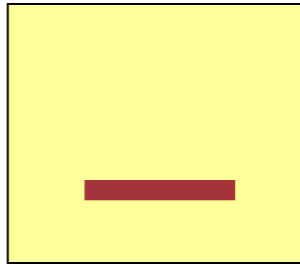


C. Roeloffzen et al., "Low-Loss Si_3N_4 TriPleX Optical Waveguides: Technology and Applications Overview," IEEE JSTQE, 2018

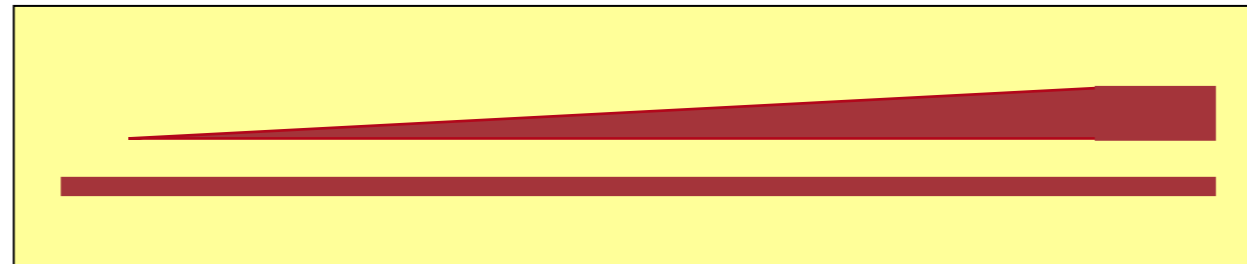


Tapering: High ⇔ Low Index Waveguides

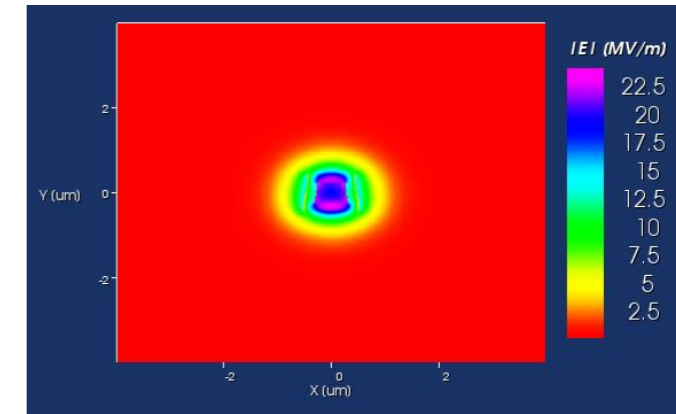
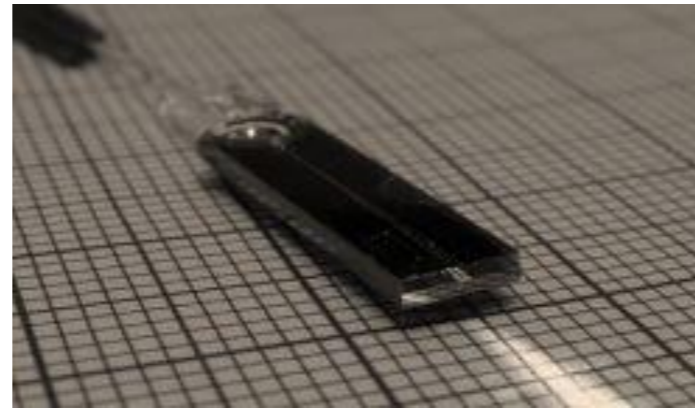
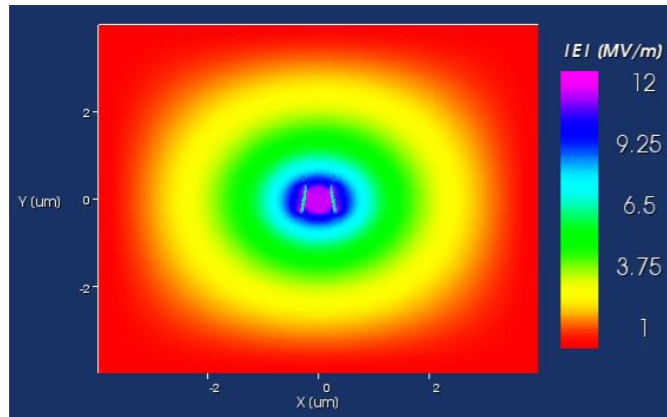
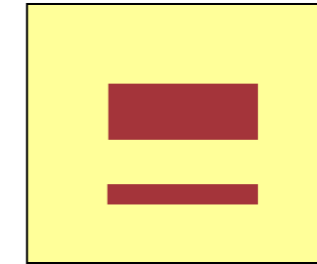
Low index contrast



Taper region



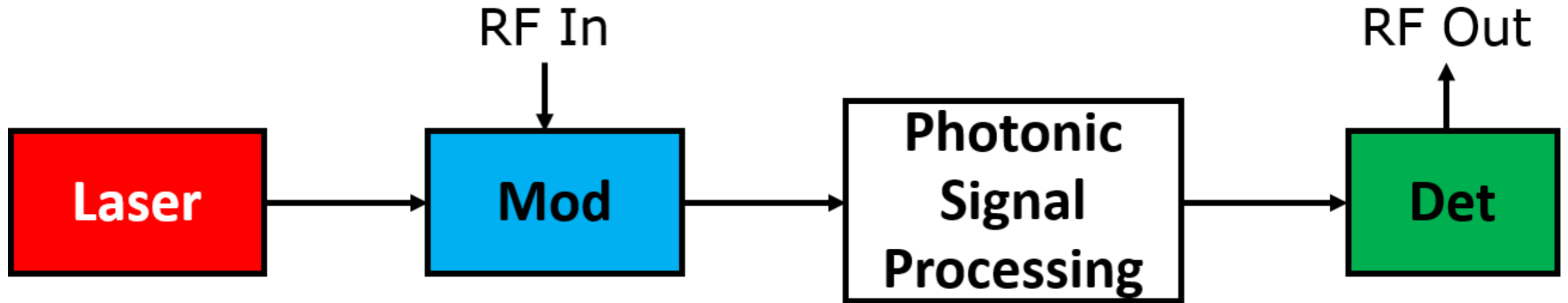
High index contrast



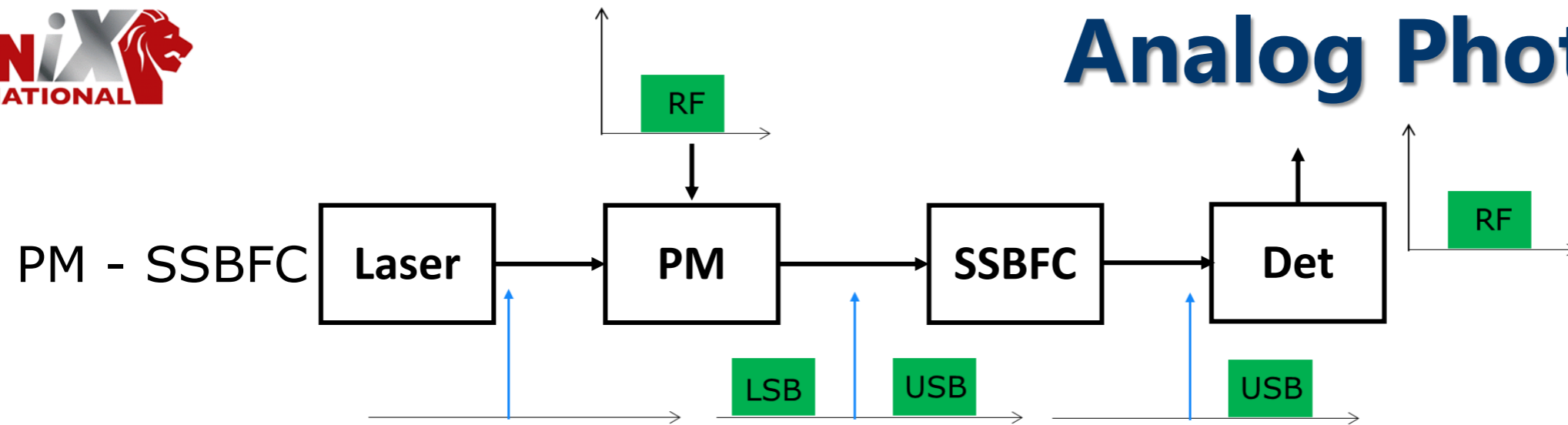
- Mode profiles from 1 μm - 10 μm
- Modefield conversion
- Pitch conversion by mask layout
- Low loss coupling to almost any external component, including SM fiber, InP and Si (SOI)



Microwave Photonic Link (MPL)



Analog Photonic Link



$$G_{PM_SSBFC} = \frac{P_{RF_out}(t)}{P_{RF_in}(t)} = \left(\frac{\pi R_{pd} P_l R}{2L V_\pi} \right)^2 = \left(\frac{\pi I_{pd_DC} R}{2V_\pi} \right)^2$$

$$I_{pd_DC}(t) = R_{pd} \frac{P_l}{L}$$

P_l = Laser power (**100 mW**)

V_π = half-wave voltage of the phase modulator (**2 V**)

L = loss of the optical link (**10 dB**)

R_{pd} = Responsivity of the photodiode (**0.8 A/W**)

R = matching resistance (**50 Ω**)

I_{pd_DC} = Average photo current (**8 mA**)

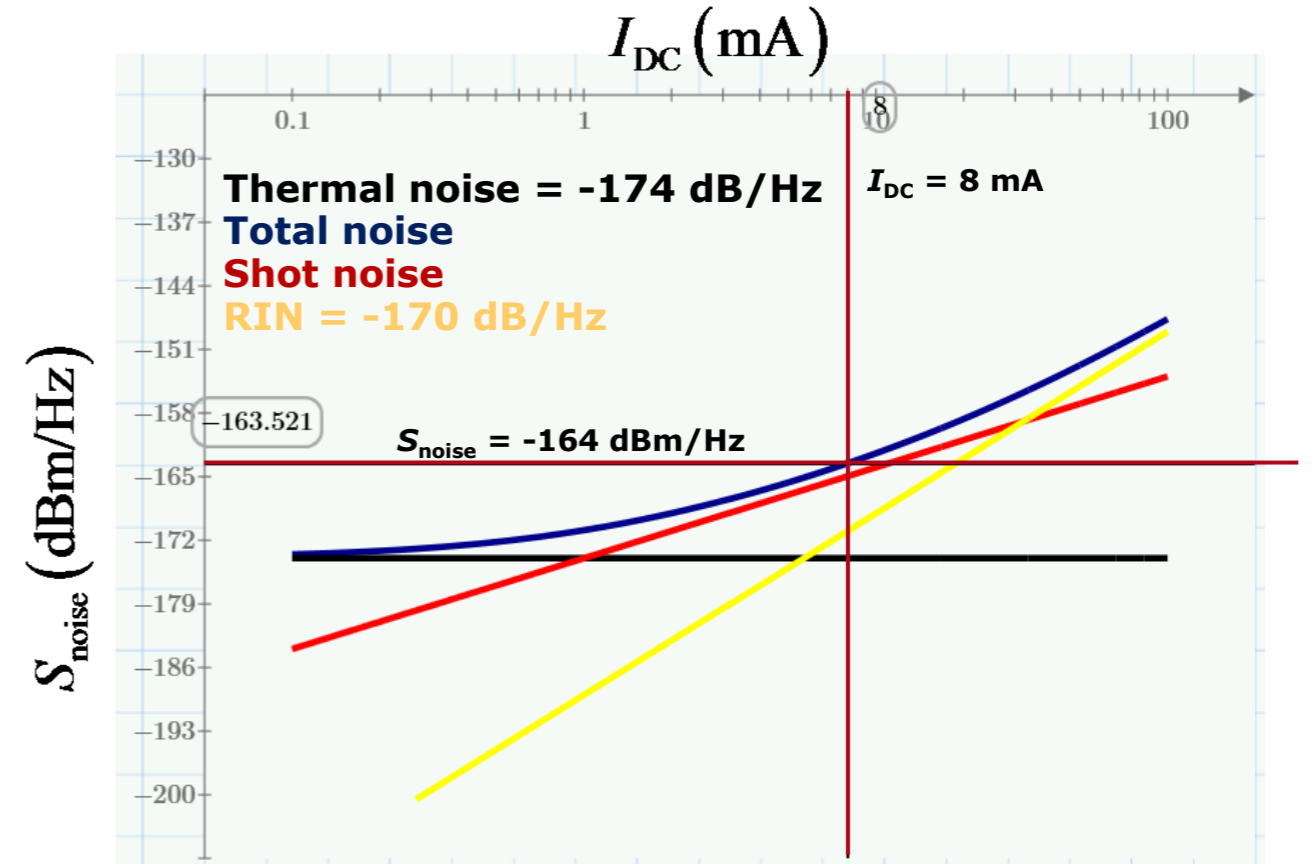
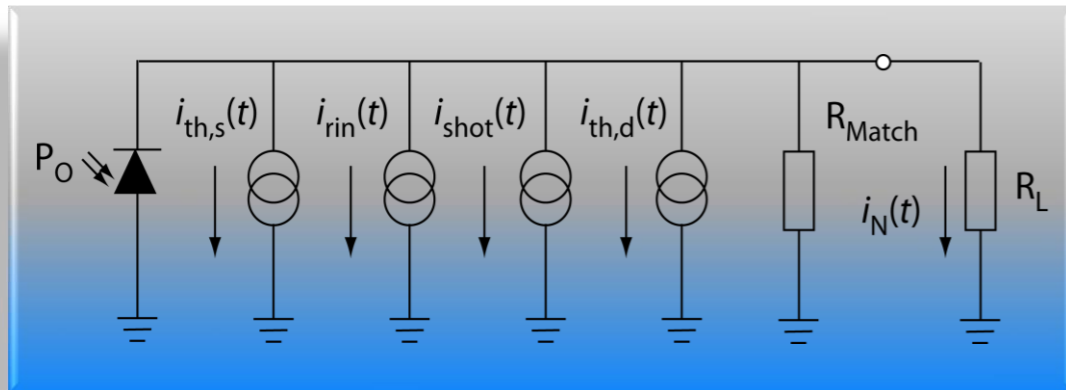
For given values: $G = \mathbf{-10\ dB}$



- Thermal noise: $S_{th} = kTB$ ($= -174 \text{ dBm} + 10 \log B @ 290\text{k}$)
- Shot noise \rightarrow **proportional to optical power (P_{opt})**: $S_{shot} = 2qI_{av}BR_L$
- Relative intensity noise (RIN) \rightarrow **proportional to (P_{opt})²**: $S_{RIN} = 10^{\frac{RIN}{10}} I_{av}^2 BR_L$
- $P_{av} = I_{av} / r_{PD}$

B = noise bandwidth
 k = Boltzmann constant ($1.38 \cdot 10^{-23}$)
 T = temperature
 q = electron charge
 r_{PD} = photodetector responsivity (A/W)
 I_{av} = average photocurrent
 P_{av} = average received optical power
 R_L = load resistance (50 ohm)

Noise modeled as current sources



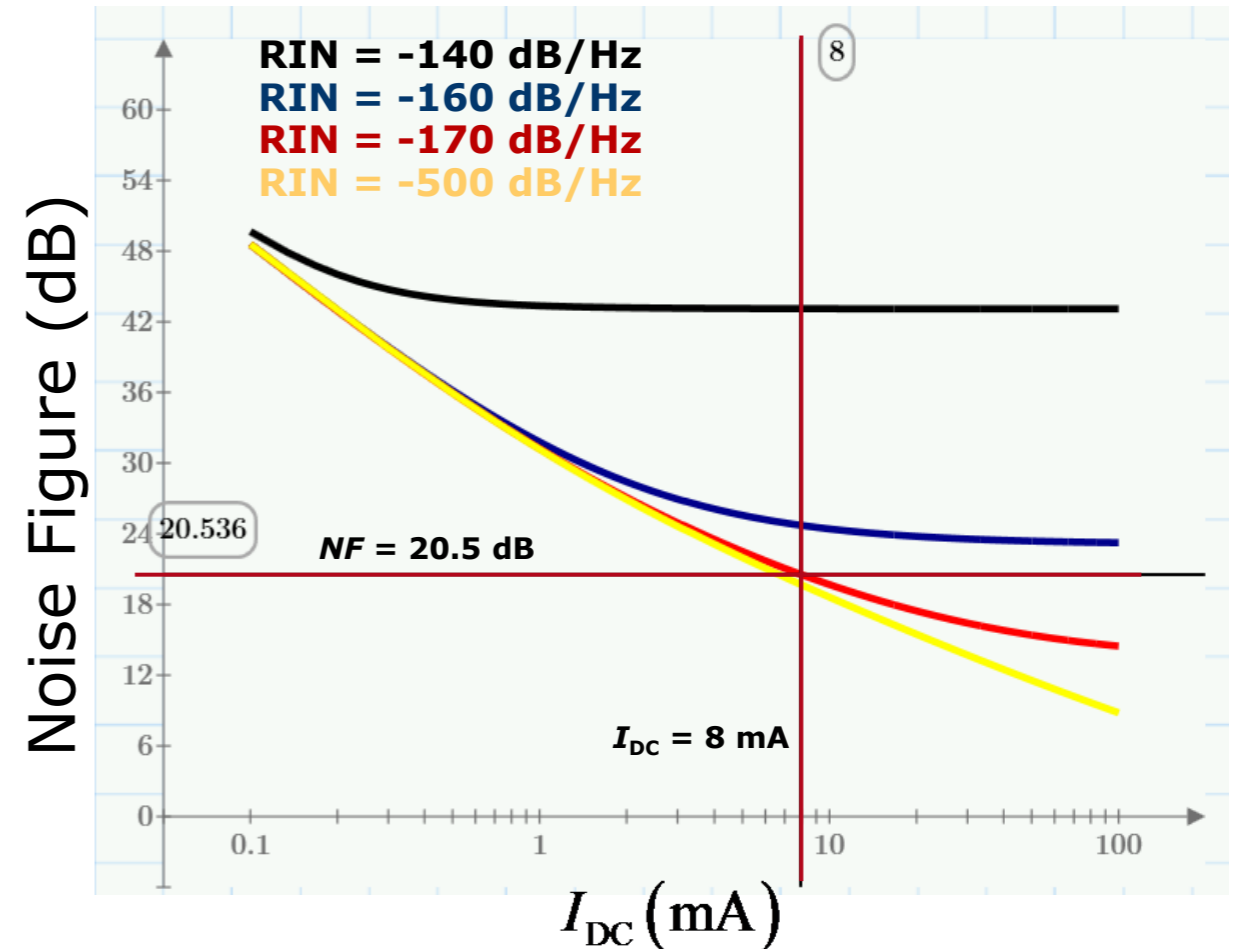
$$S_{\text{noise}} = S_{\text{th}} + \frac{1}{4} (S_{\text{shot}} + S_{\text{RIN}})$$

$$\text{NF} = 10 \log_{10} \left(\frac{S_{\text{noise}}}{G_{\text{link}} k_B T B} \right)$$

$$\text{NF} = S_{\text{noise}} (\text{dBm/Hz}) - G_{\text{link}} (\text{dB}) + 174 \text{ dBm/Hz}$$

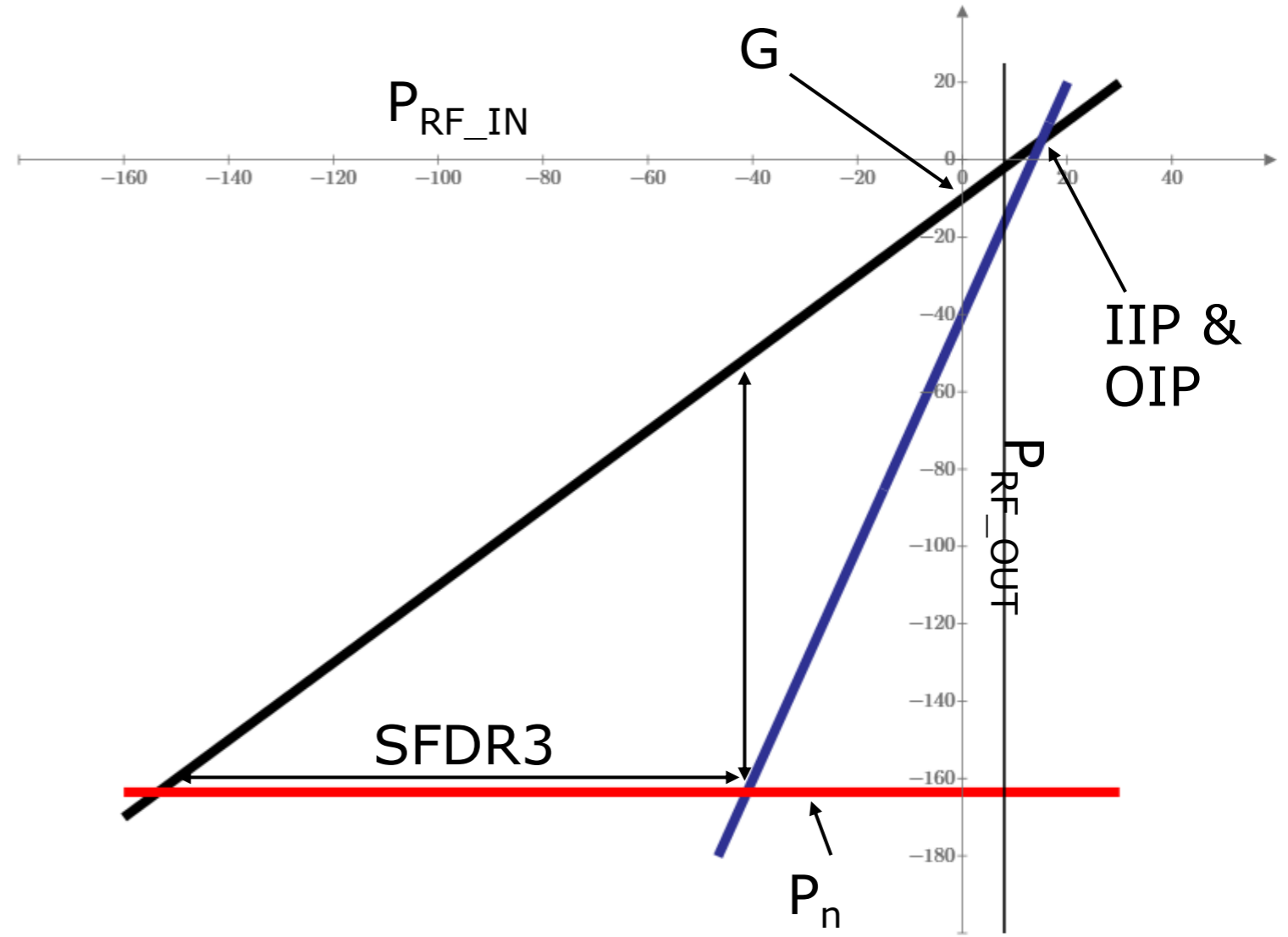
- High Noise Figure
- $I_{\text{DC}} \uparrow \rightarrow \text{NF} \downarrow$ until RIN limitation
- Minimum NF depends on RIN

$L_m = 10 \text{ dB}$ $r_{\text{PD}} = 0.8 \text{ A/W}$
 $V_{\pi} = 2 \text{ V}$ $R_L = 50 \Omega$



Spurious-Free Dynamic Range

- PM-SSBFC
- Laser power = 100 mW
- Detected optical power = 10 dBm
- Photodiode current 8 mA (matched load)
- RIN = -170 dB / Hz
- $V_{\pi} = 2 \text{ V}$
- $P_{in_1dB} = 6 \text{ dBm}$
- Gain = -10 dB (P_{out} @ $P_{in} = 0 \text{ dBm}$)
- OIP3 = 5 dBm
- IIP3 = 15 dBm
- $P_n = -164 \text{ dBm/Hz}$
- NF = 20 dB
- SFDR3 = $112 \text{ dB}\cdot\text{Hz}^{2/3}$



Multiple Indium Phosphide Chips

- **Gain**
 - High power laser (> 50 mW)
 - High power gain (> 100 mW)
 - Small linewidth (< 10 kHz)
 - Low RIN (-170 dBc / Hz)
- **Modulator**
 - Phase modulator
 - High speed (> 40 GHz)
 - Sensitive ($V_{\pi} < 3$ V)
- **Detectors**
 - High speed (> 40 GHz)
 - Responsivity (> 0.6 A/W)
- Very low RF crosstalk required (< -70 dB)

TriPleX, Silicon Nitride chips

- Tunable mirror for laser
- Rectangular filter for SSBFC
- High contrast, low loss optical processing
- Spot size converters for low loss interfacing

- High integration density +
- Efficient, low-power tunability
- Drives Co\$t Down

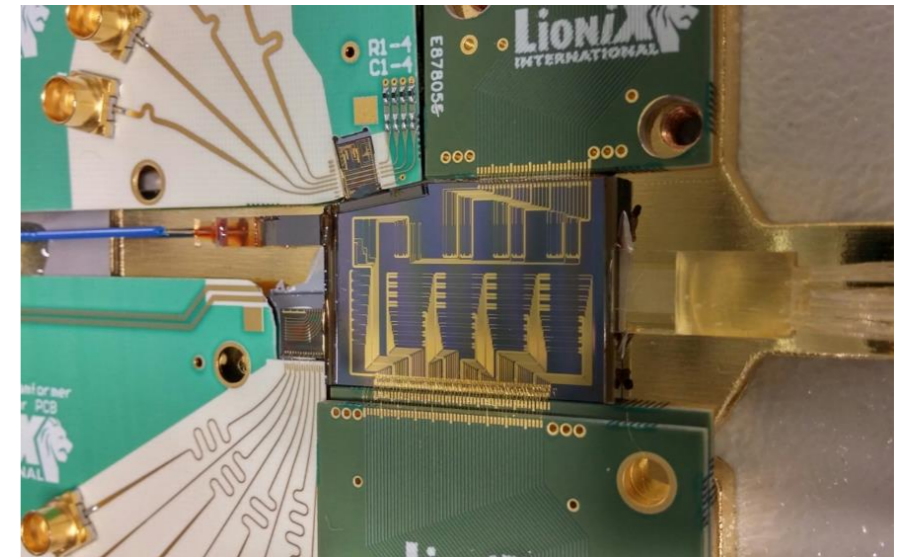
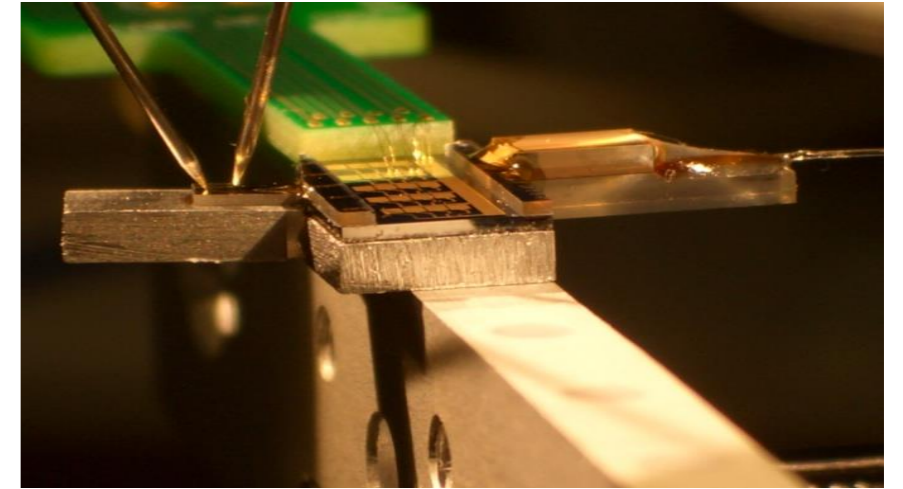


- **TriPleX (Si_3N_4)**

- ✓ Ultra low loss (<0.1 dB/cm)
- ✓ Applicable in almost all interesting wavelength regions
- ✓ Reliable actuators (heaters, strain-based: PZT)
- ✗ But is not electro-optic, so lacks direct light generation, high speed modulation and detection

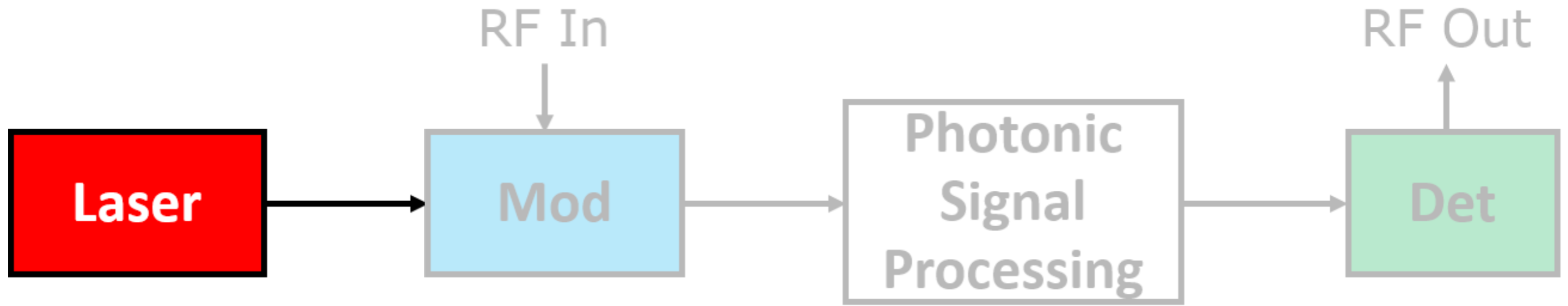
- **Hybrid integration TriPleX with InP yielding:**

- ✓ Very high quality, widely tuneable lasers !
- ✓ High speed modulation (E/O conversion)
- ✓ High speed photodetection (O/E conversion)
- ✓ Hybrid integration with other materials (AlGaAs, Si, etc.) was shown
- ✓ Intrinsically stable, vibration insensitive

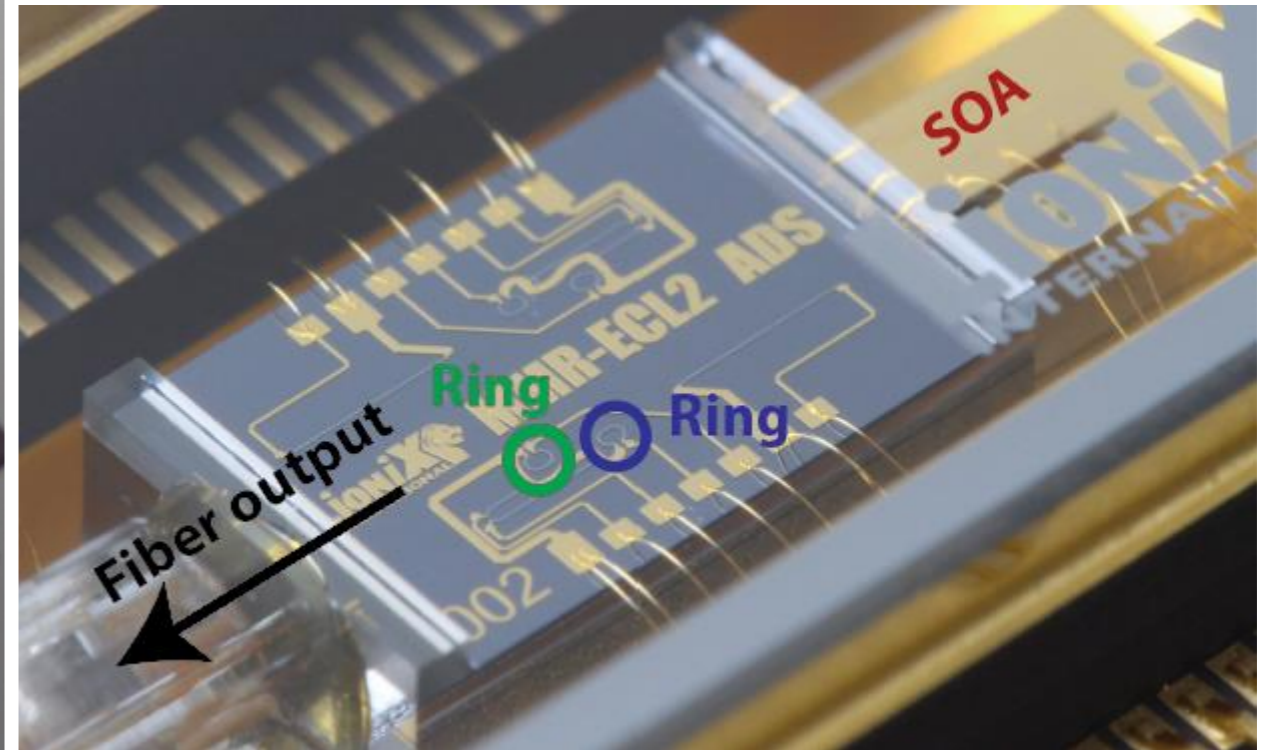
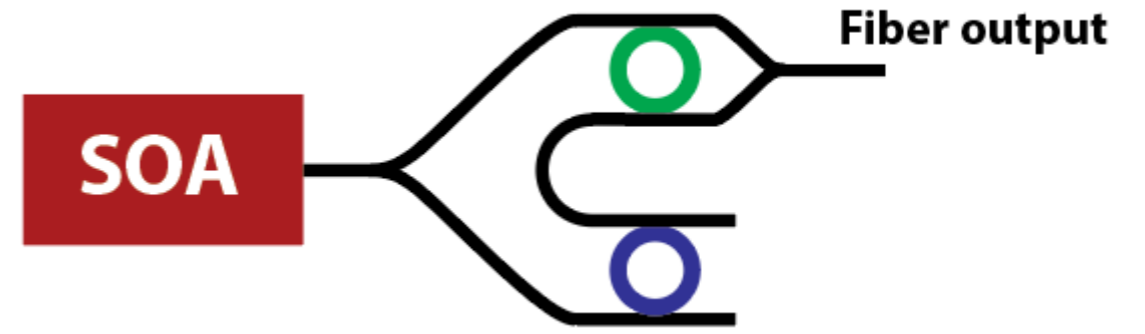
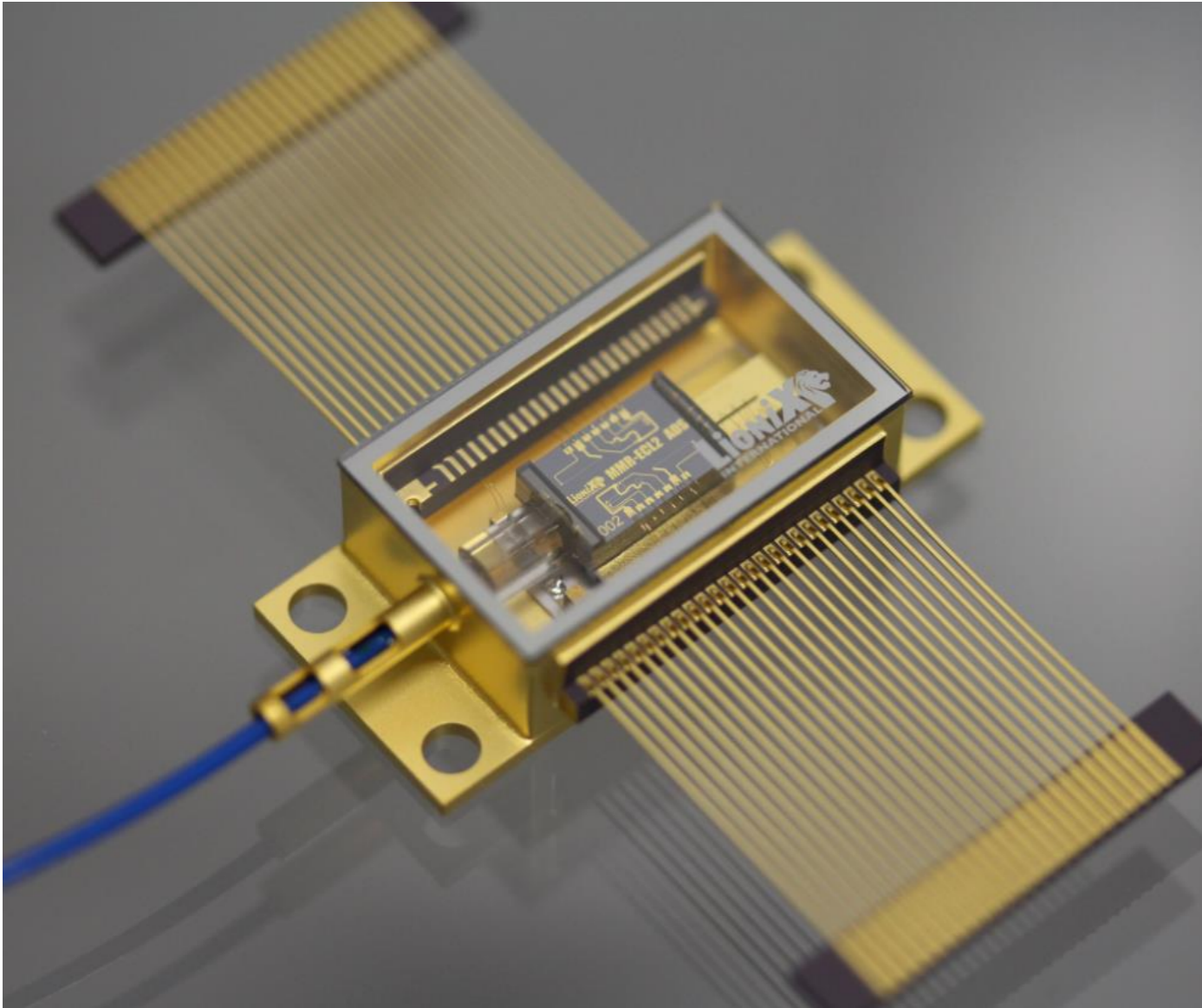


D. Marpaung et al., "Integrated microwave photonics," LPR, 2013



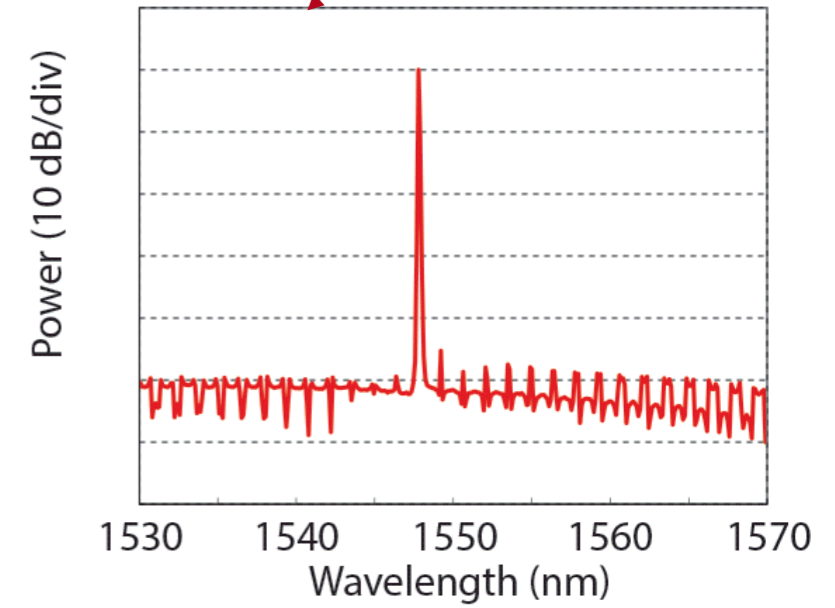
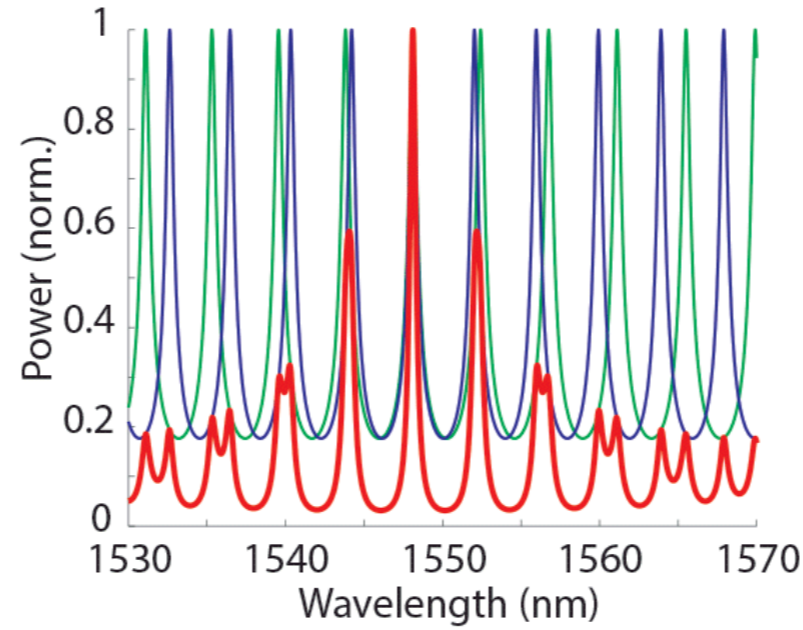
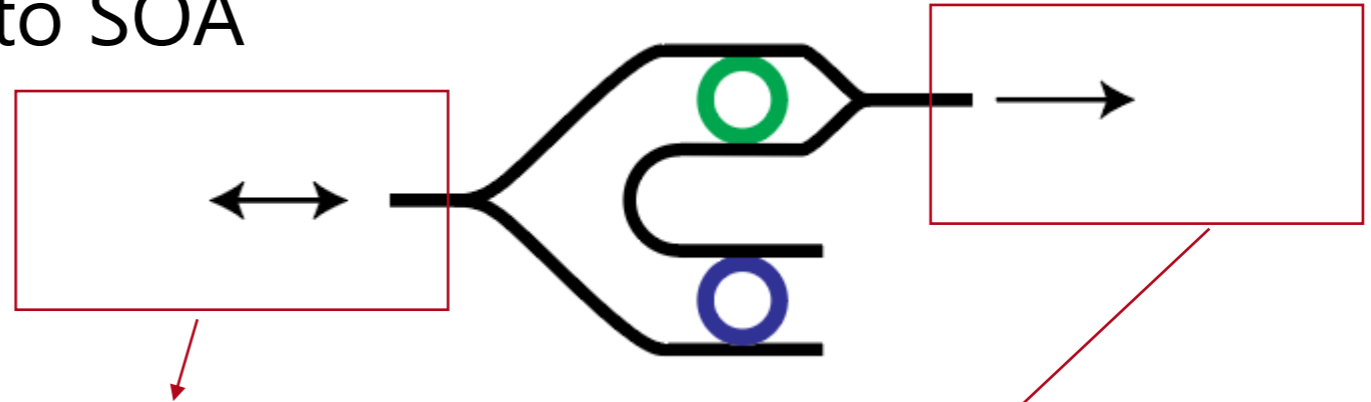


Laser Assembly

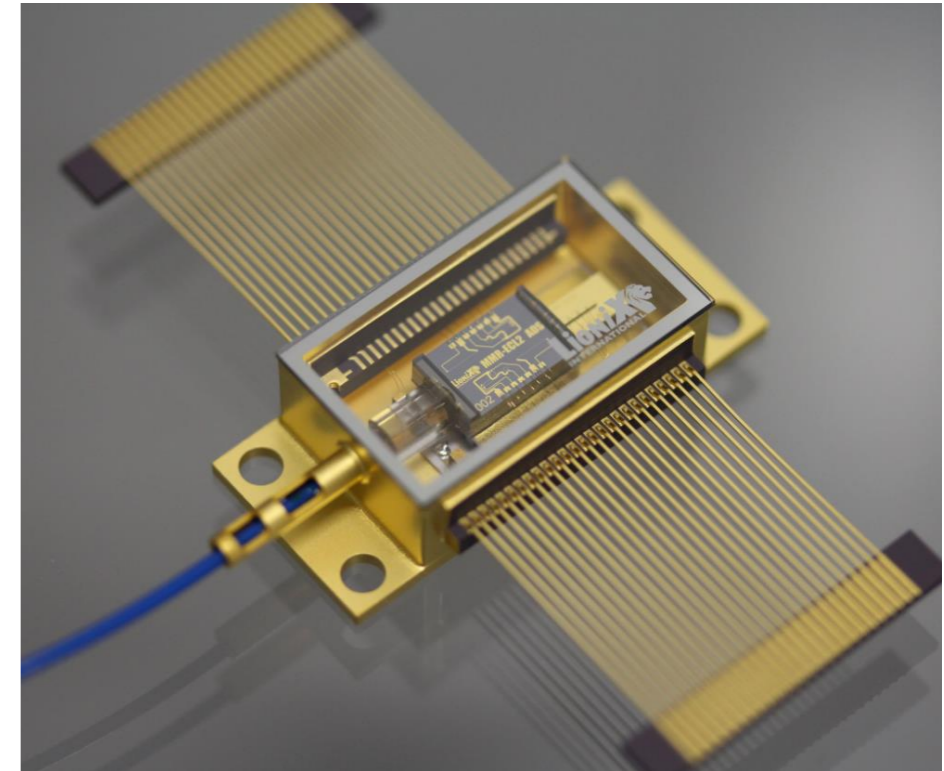


- Double ring reflector, attach to SOA

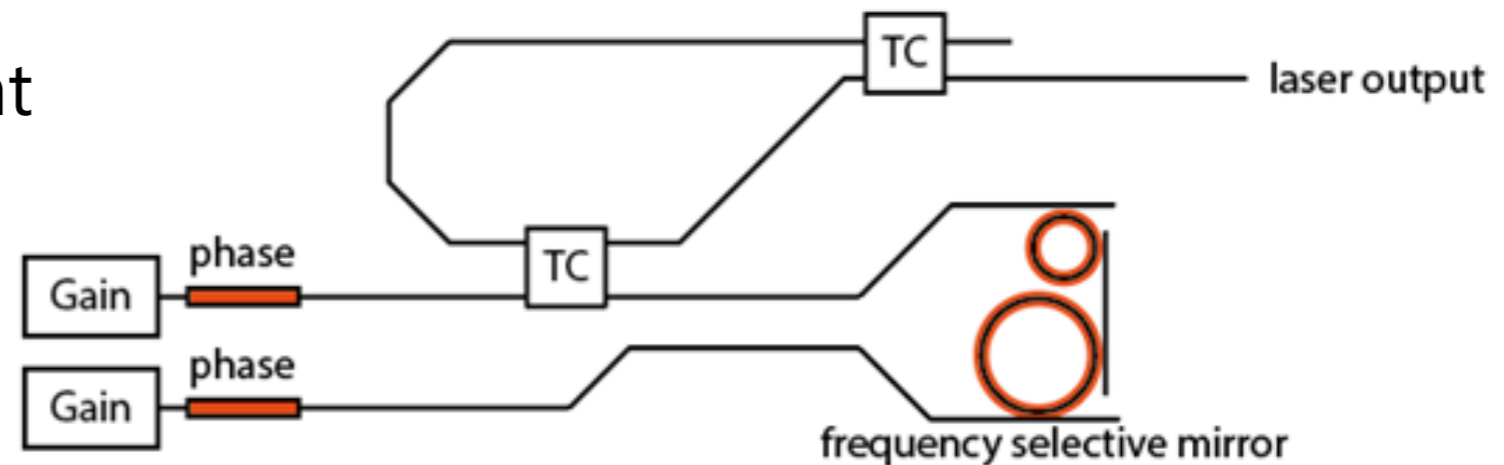
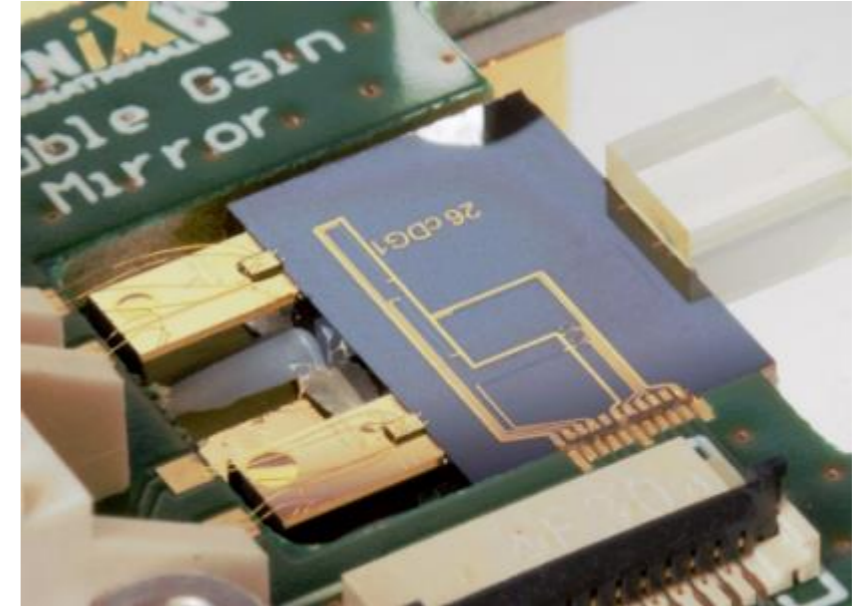
Heating 1 ring
Causes spectrum
to hop across
wavelengths



- Output power > 17 dBm (50 mW)
 - Maximum power 20 dBm (100 mW)
- Linewidth < 1 kHz
- Wavelength tuning over c-band
 - 80-100 nm tuning range available
- Millisecond switching speed
 - 0.5 ms wavelength-to-wavelength switching
- SMSR > 40 dB
- RIN < -170 dBc/Hz
- Mode-hop free tuning range 0.2 nm

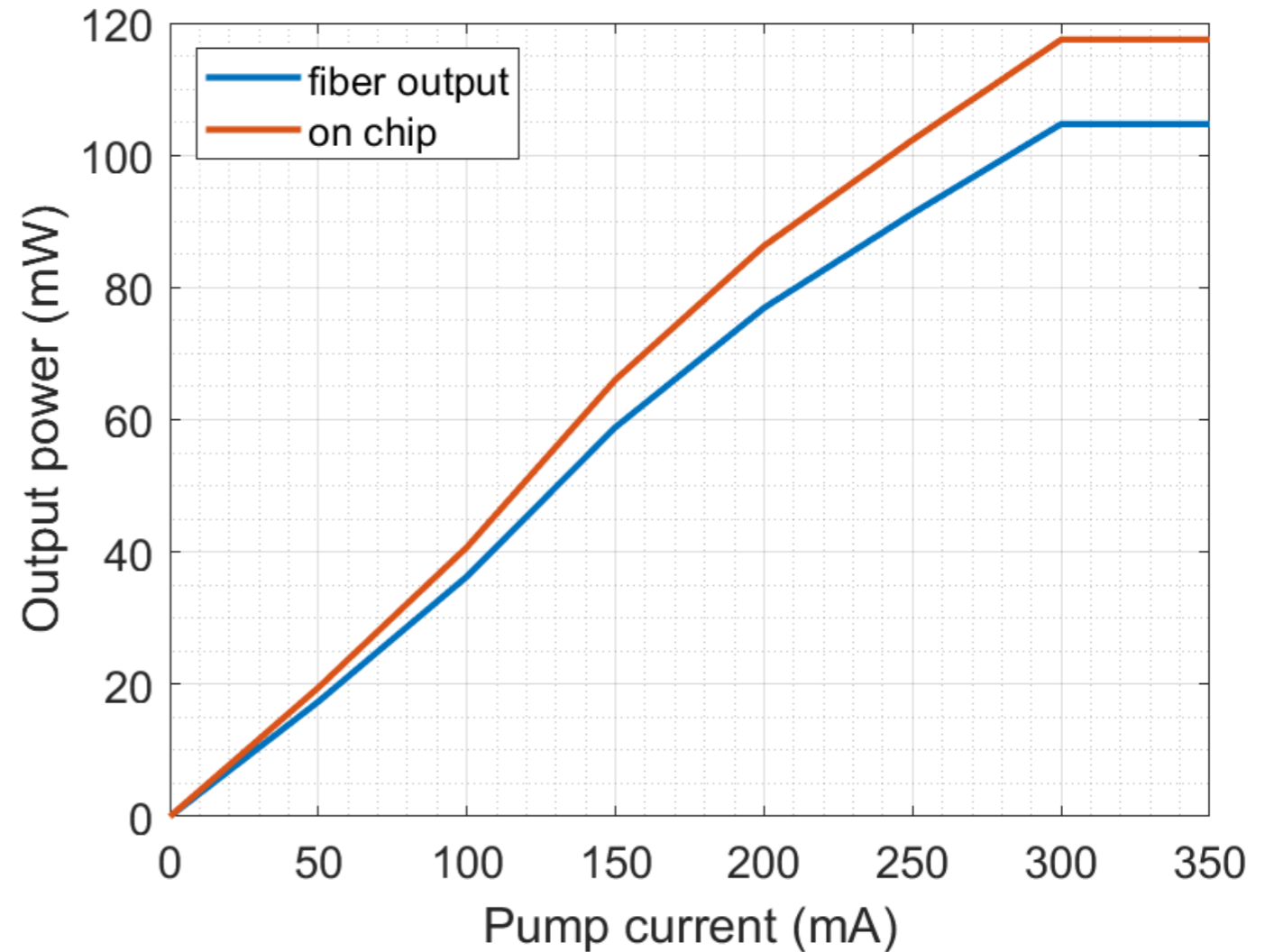


- Use two InP gain sections sharing a cavity
 - But maintaining single gain properties
- Output coupling controlled by tunable coupler (TC)
- Output coherently combined
- Highest output power achieved at 80% output coupling



Output Power 100 mW!

- Output power: **>100 mW** (20 dBm); 117 mW on chip
- Laser was in single mode
- Side-mode-suppression ratio > 50 dB
- Gain saturation begins above 300 mA
- Improved thermal conductivity will increase the output power even more

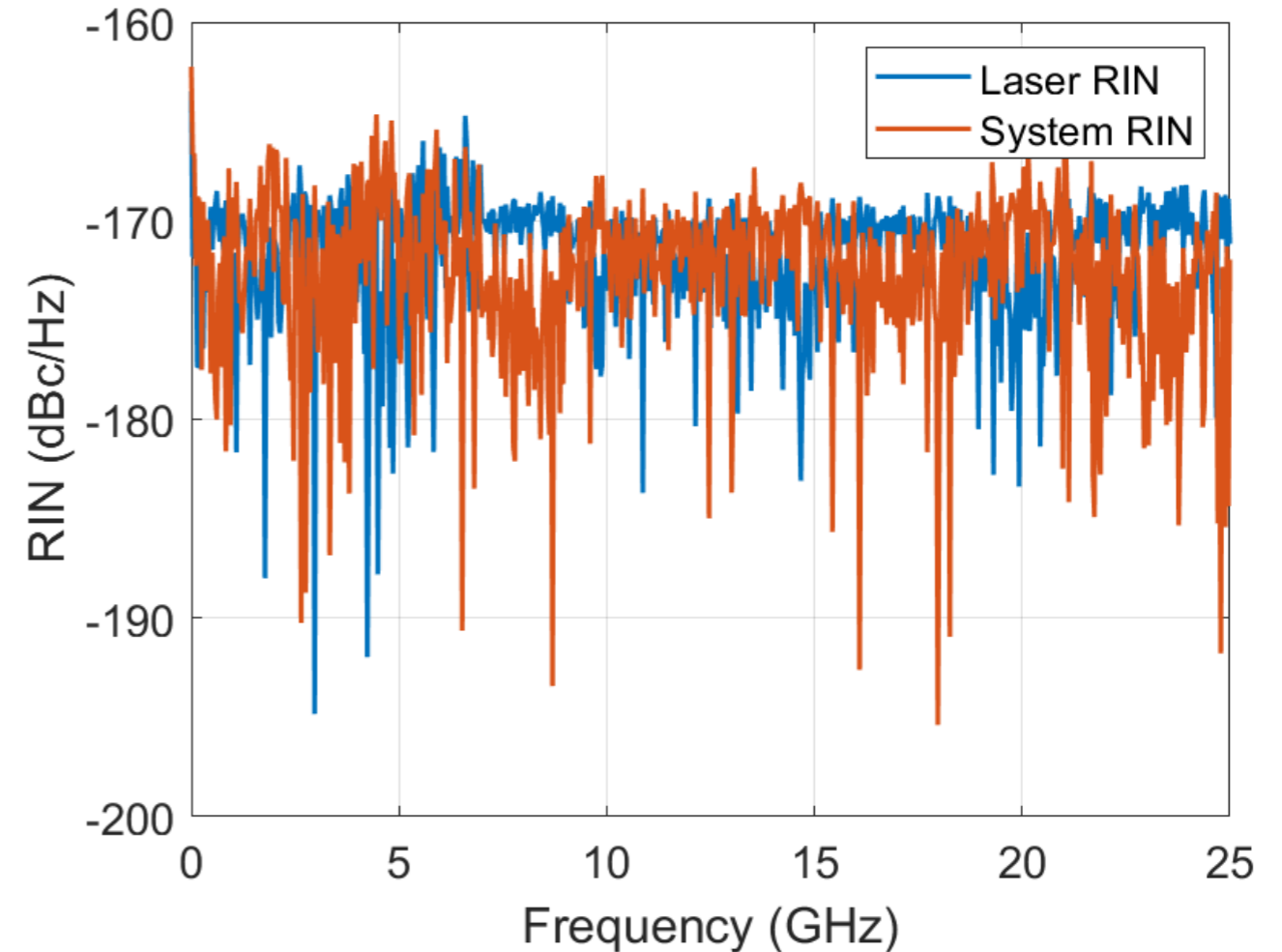


J. Epping et al., "High power integrated laser for microwave photonics," OFC, 2020



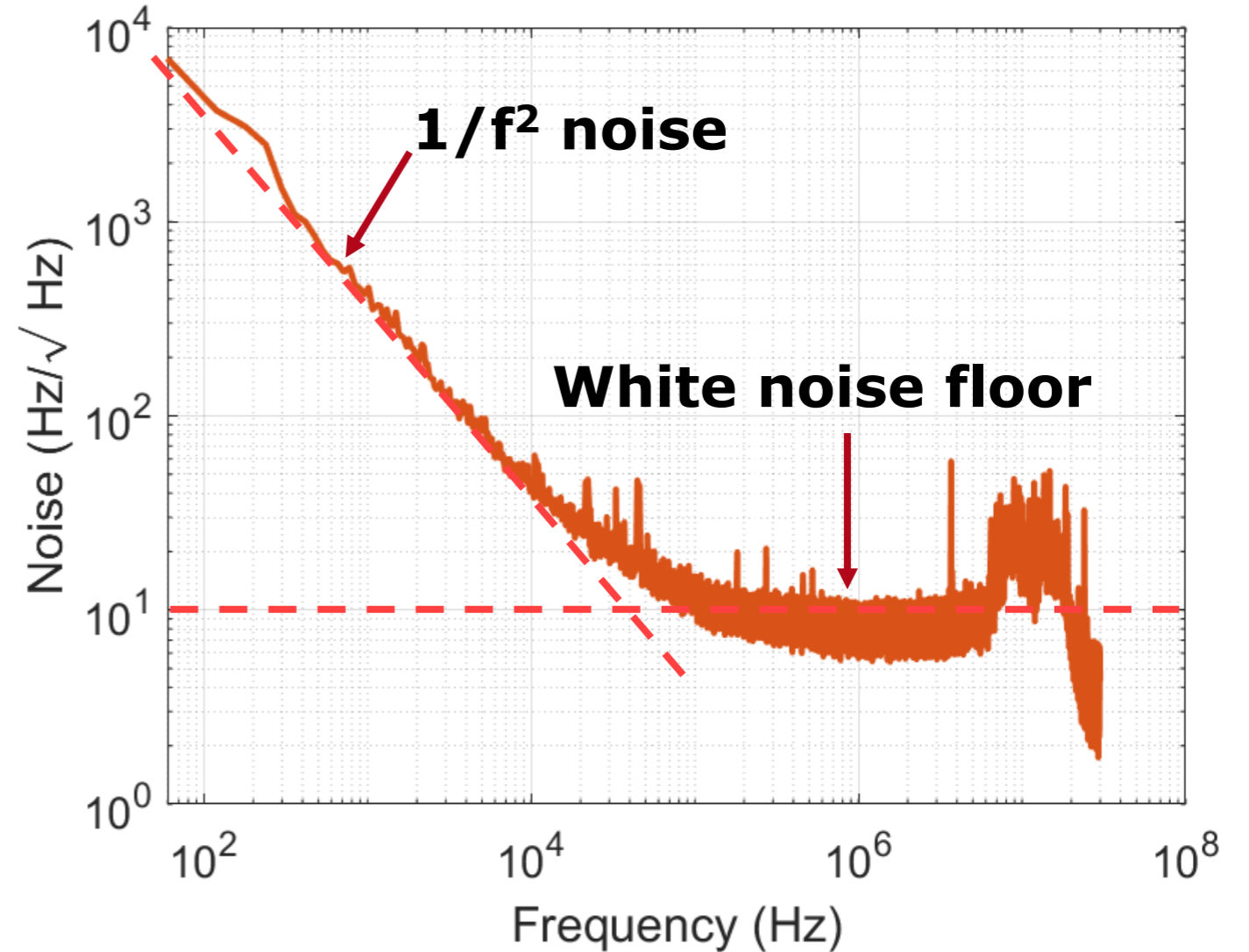
Low Relative Intensity Noise

- Low relative intensity noise (RIN) is crucial microwave photonic links
- RIN results in signal noise
- Low RIN achieved
 - Measurement limited

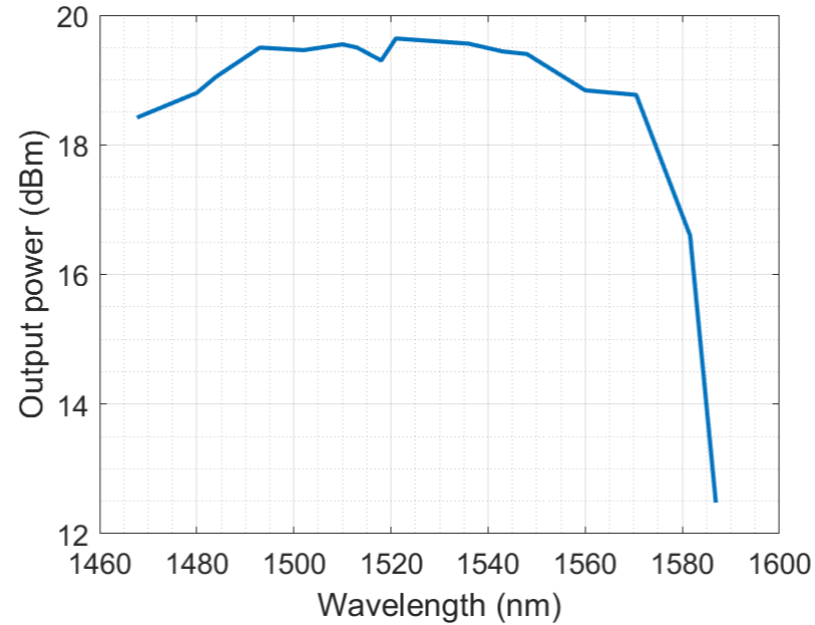
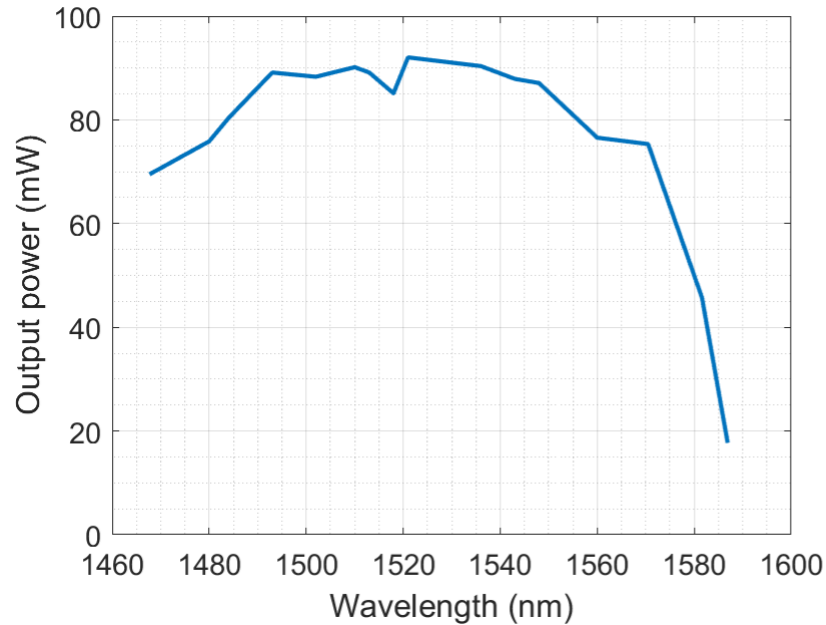


- White noise floor (NF) gives intrinsic linewidth:
 - Linewidth $\approx \pi \cdot (\text{NF})^2 \approx 320 \text{ Hz}$
- Noise at higher frequencies are measurement artifacts.
- Propagation losses: 0.08 dB/cm

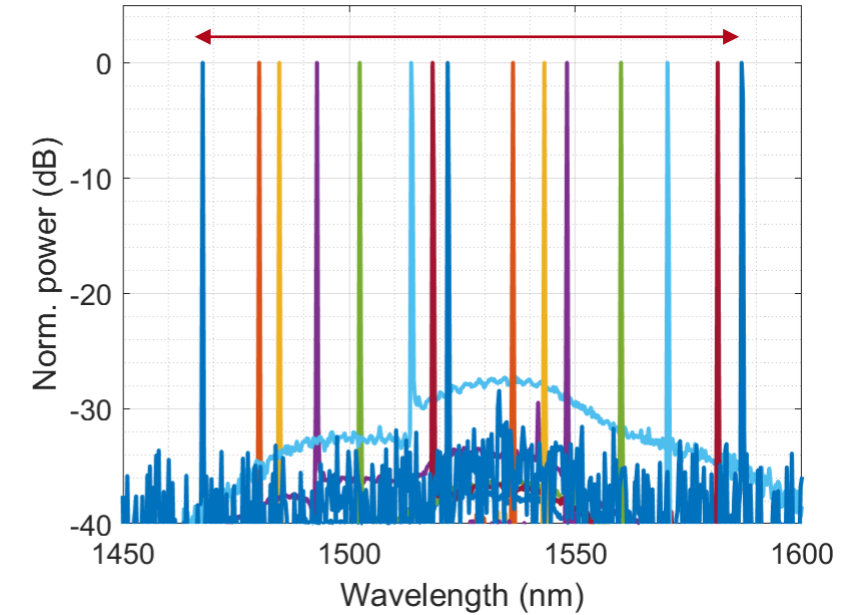
Low Frequency Noise



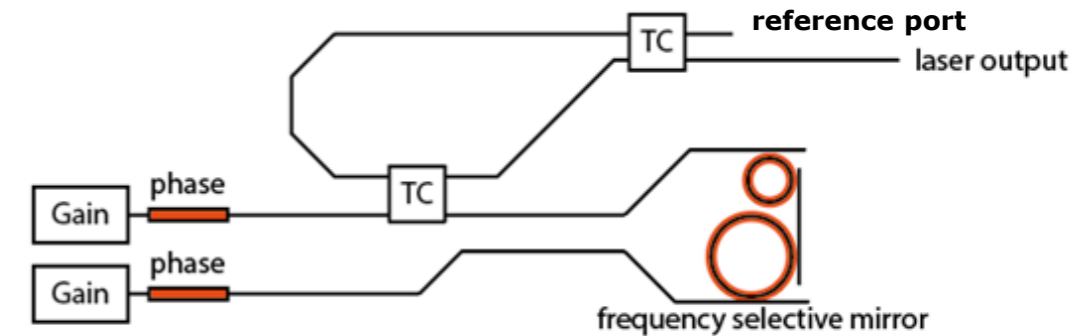
Output power @ laser output



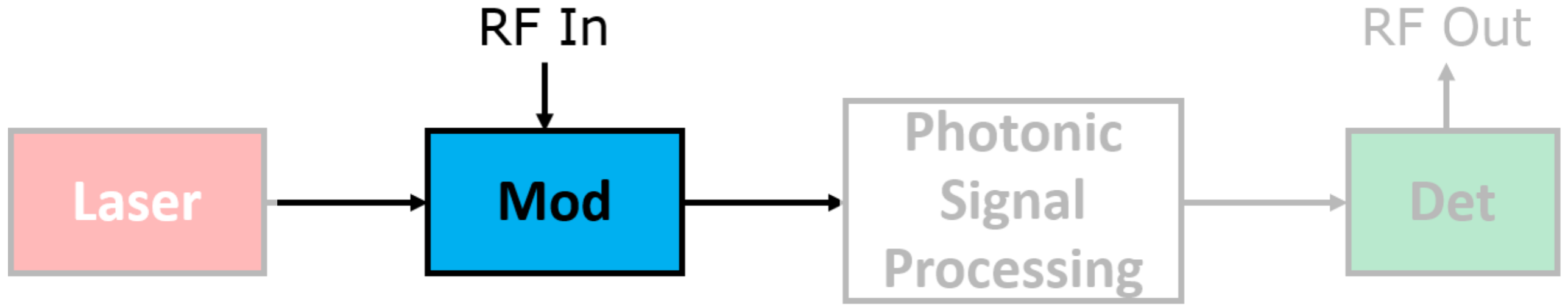
Spectrum @ reference port



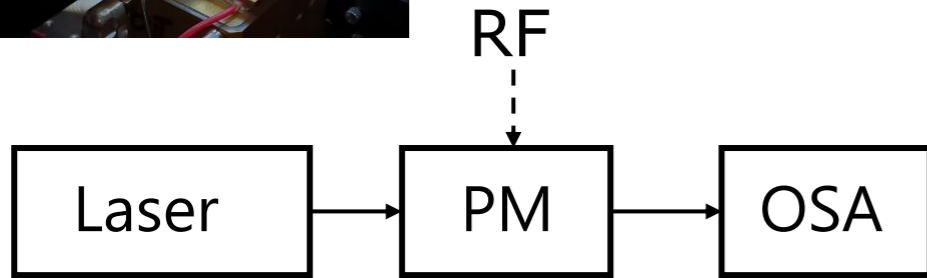
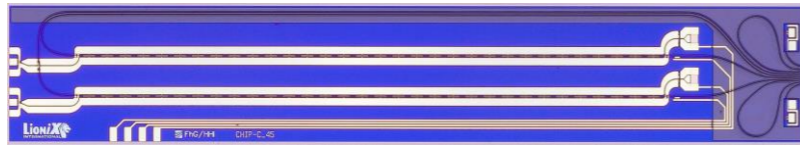
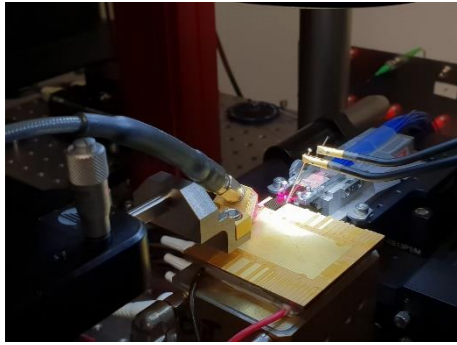
- Total tuning range is **119 nm!!!**
- 100 nm tuning range within -1dB power drop
- Tunable output coupler increases tuning range by shifting the gain spectrum



MPL: Phase Modulator



InP Modulator (E/O conversion)



Increase RF power until sidebands are as high as the carrier.

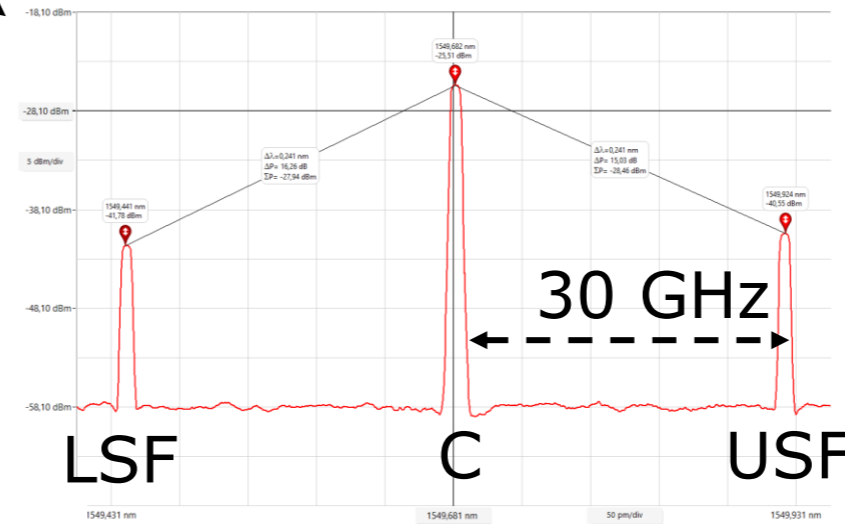
Calculate V_{π} using:

$$V_{\pi} = \frac{V_m}{0.457}$$

Where:

$$V_m = \sqrt{2P_{RF}R}$$

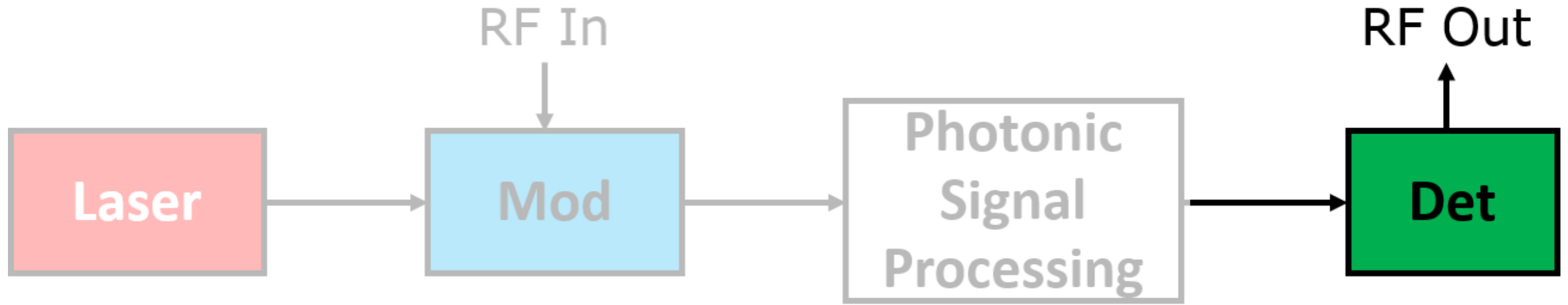
Freq (GHz)	ΔP (dB)	m	V_{π} (V)
5	10.2	0.5907	1.68
10	10.9	0.5485	1.80
20	13.2	0.4275	2.30
30	15.6	0.3275	3.00



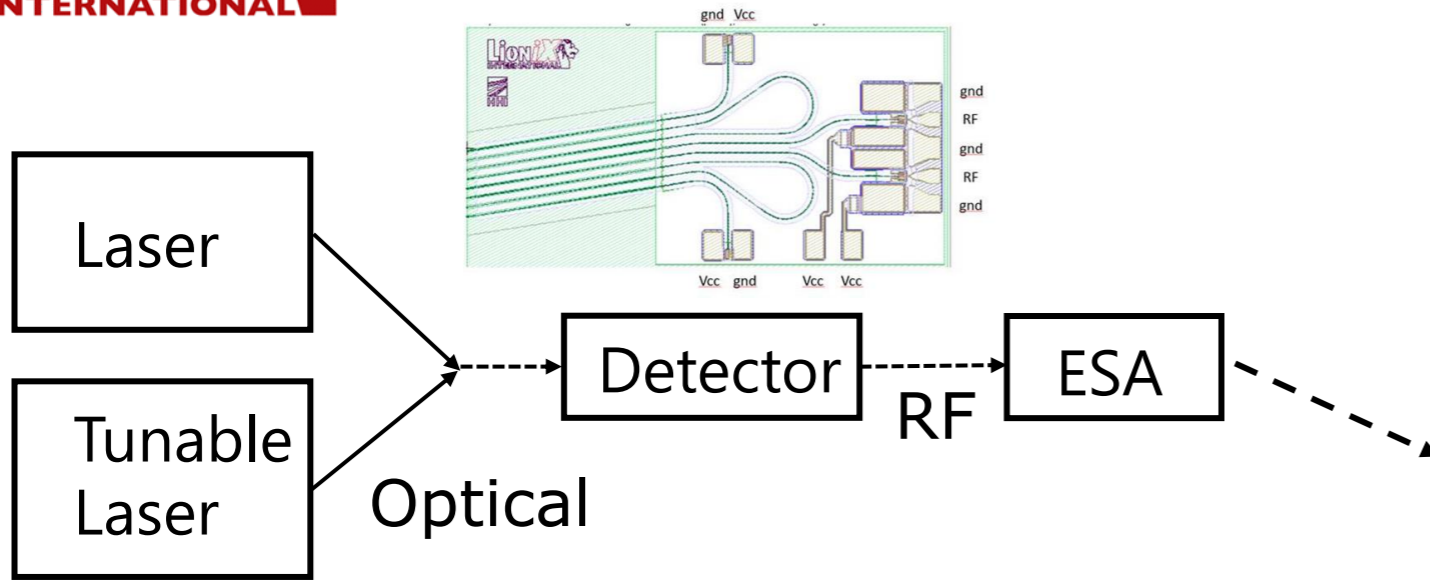
↑
VERY GOOD!

Optical spectrum analysis method (Yongqiang Shi et al., IEEE JLT 21 (10), 2003)

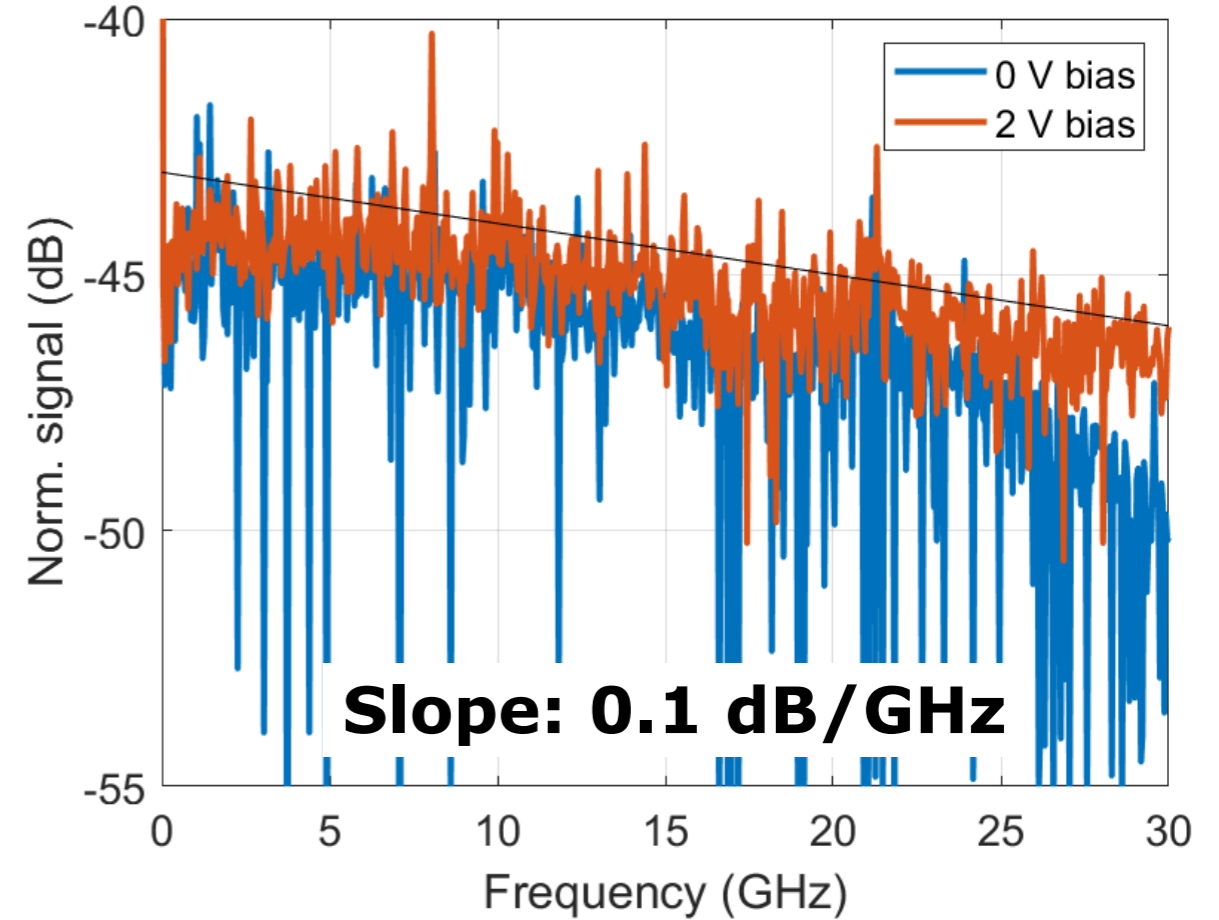


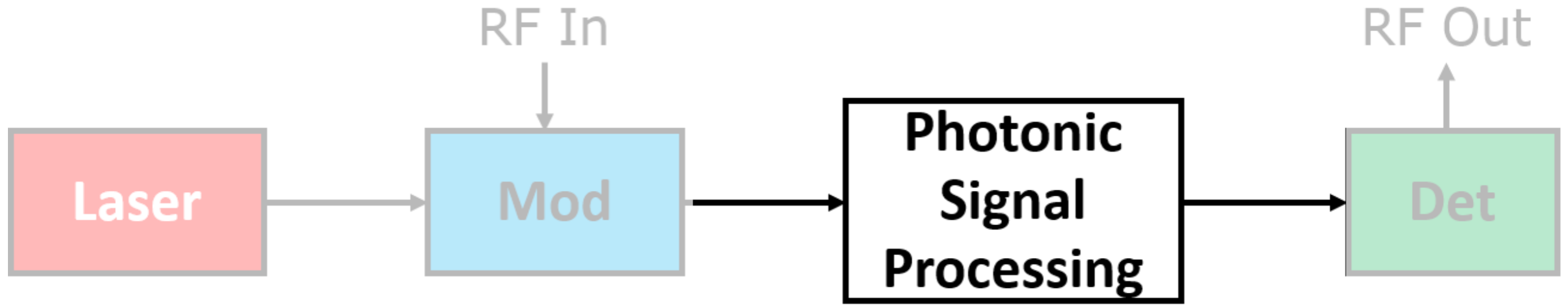


Detector Responsivity / Slope



- ✓ High speed: > **40 GHz**
- ✓ Responsivity > **0.8 A/W**
- ✓ Internal Matching and biasing network





Smart antenna for Satcom



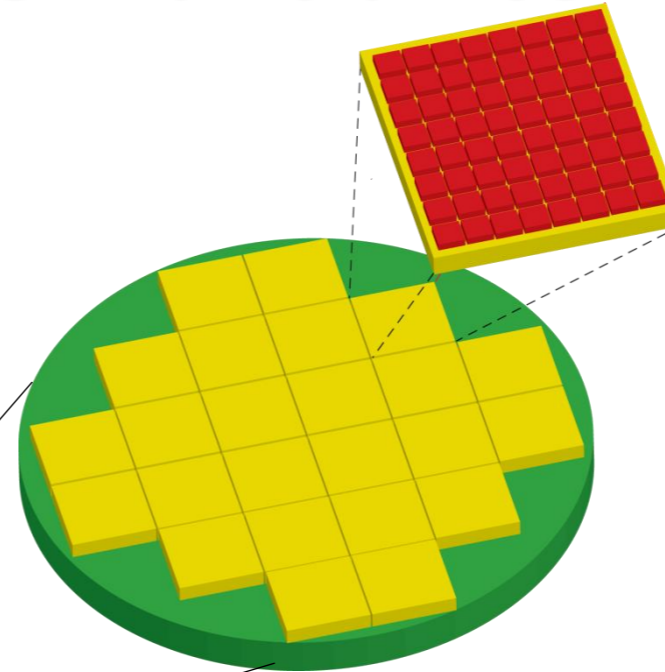
Ku-Band

Required :

Broadband,
continuous and
squint-free
beamsteering

To Receive :

Data & Digital
video
broadcasting
via satellite
(DVB-S) signal

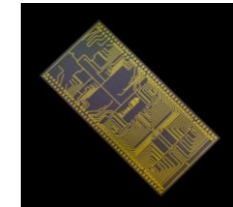


Antenna tile
(64 antenna elements)

Solution :

Phased-array
antenna with
large number
of elements

+ Photonic
beamformer

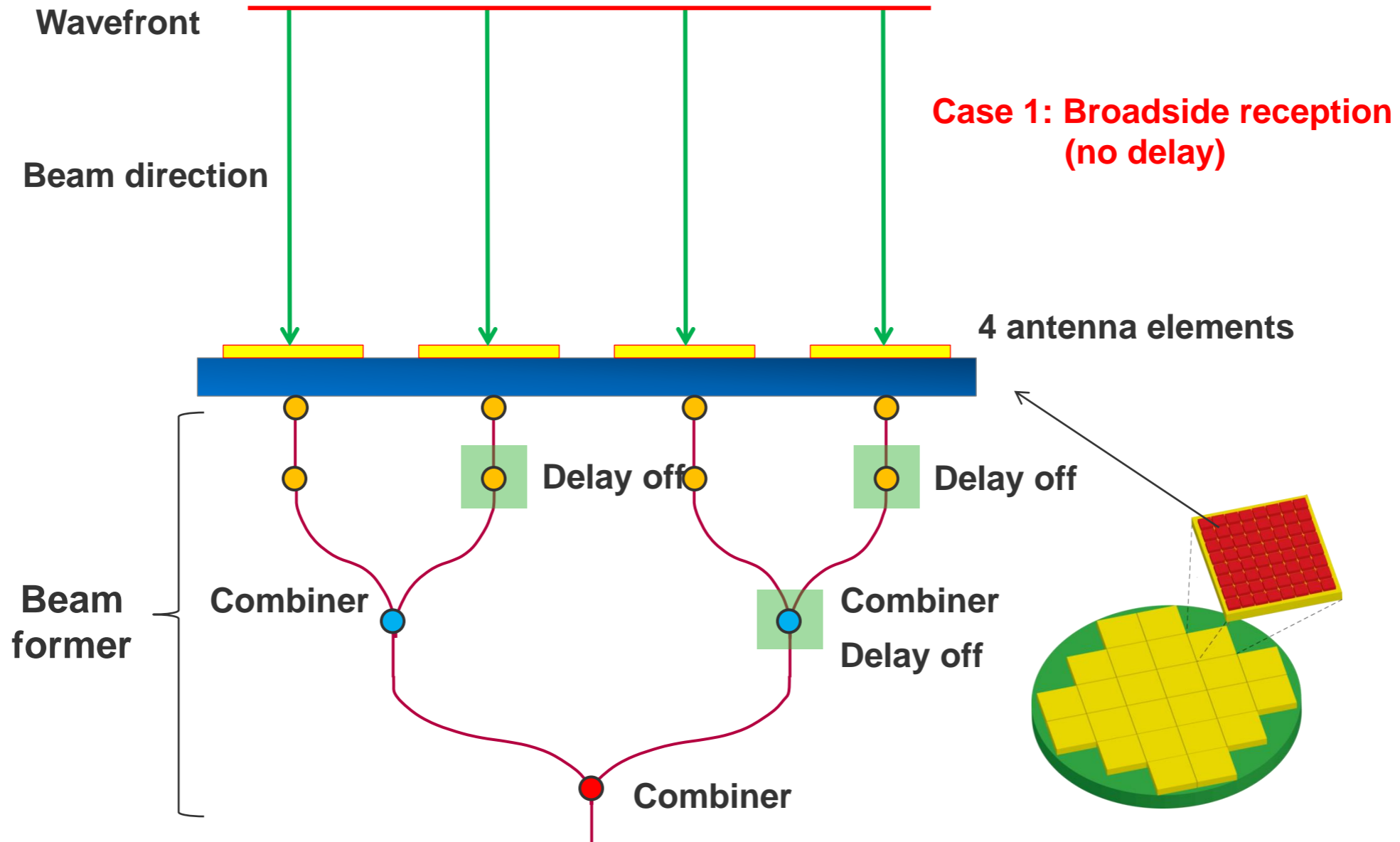


Aim:

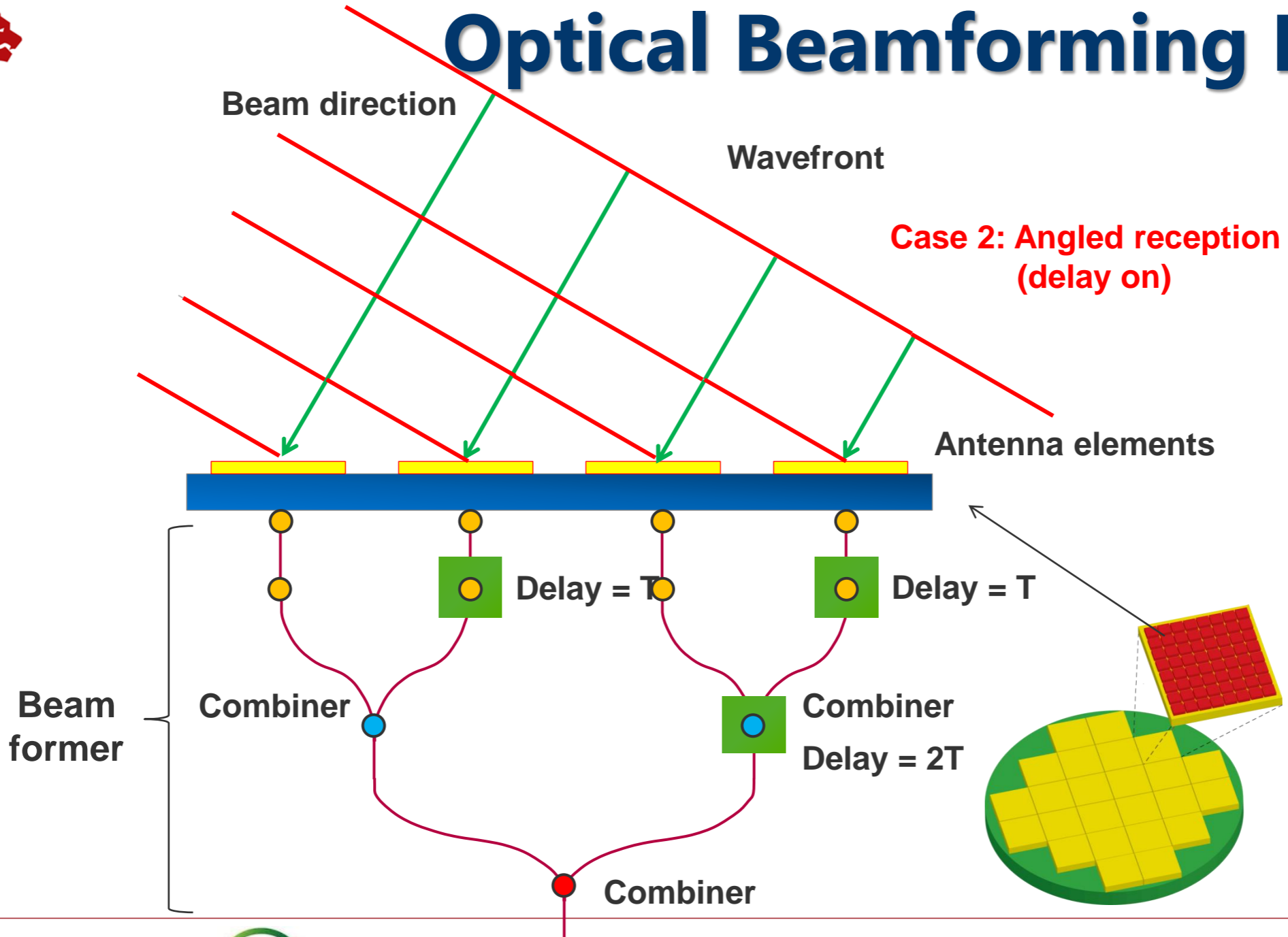
In-Flight
Entertainment:
Live television
channels and
broadband
communication at
passenger seats



Optical Beamforming Network

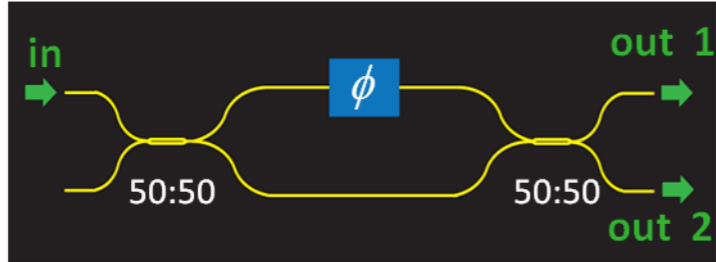


Optical Beamforming Network



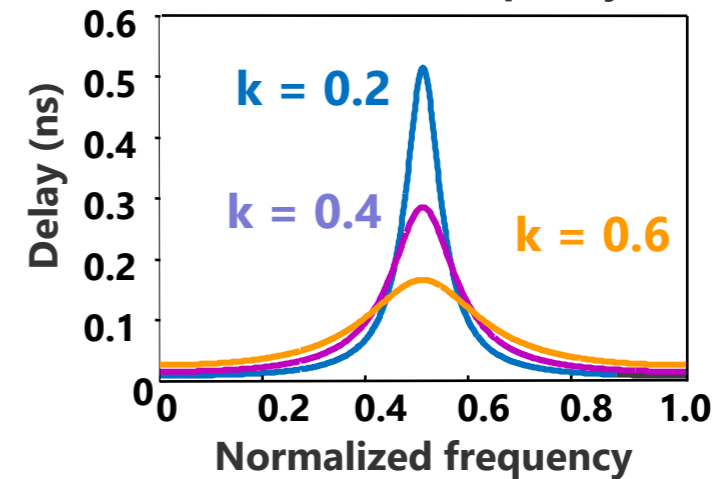
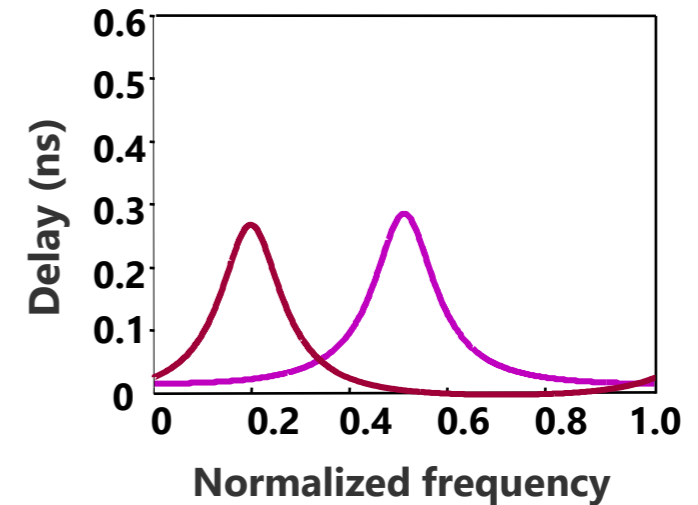
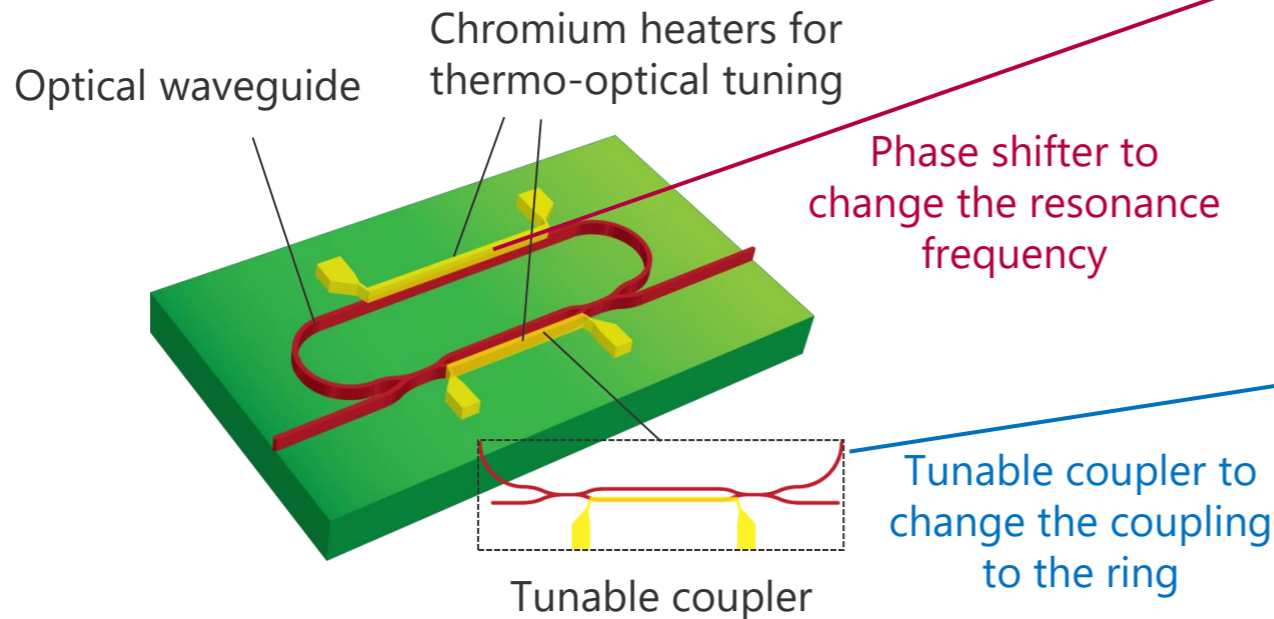
True Time Delay via Optical Ring Resonator

Combiners: Tunable MZI coupler

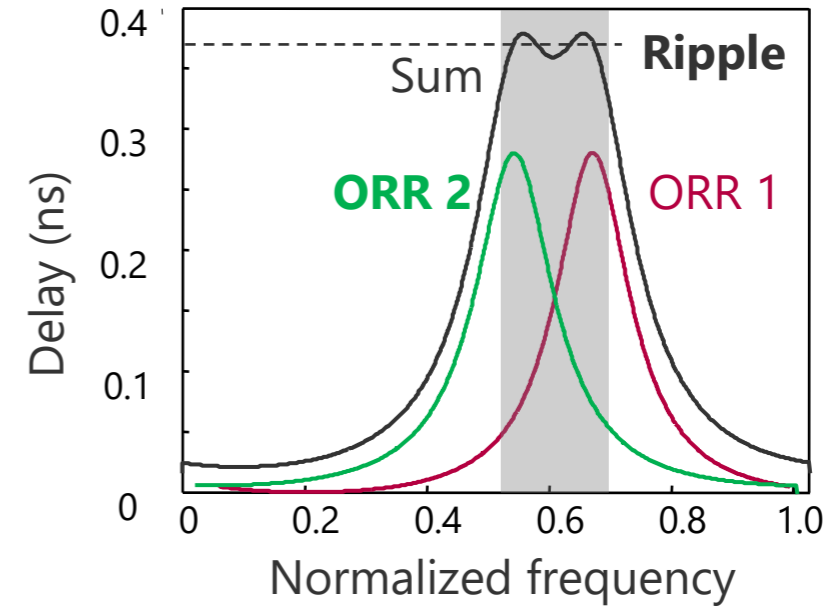
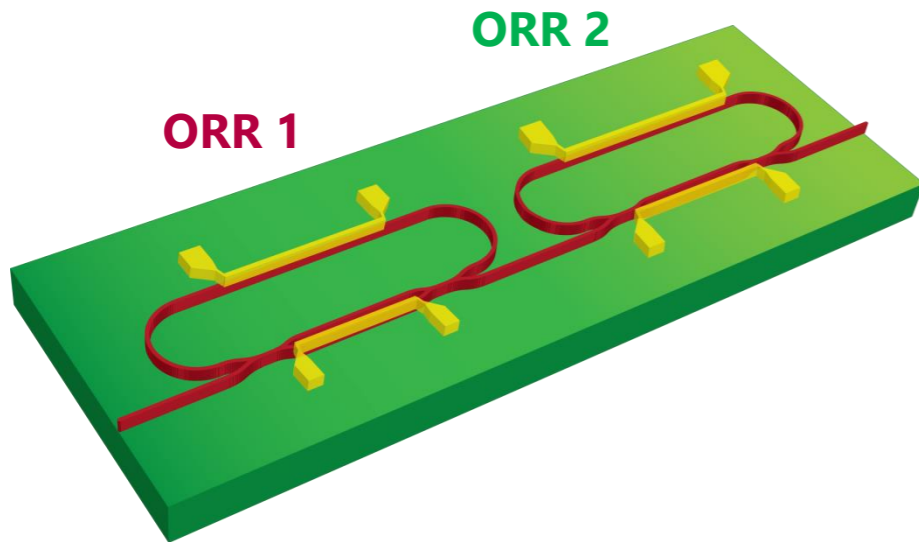


If the directional couplers are 50:50, by changing f (thermo-optic tuning) the optical power at the complementary outputs can be tuned from 0 to 100%

Delay element: Optical ring resonator



- Single ORR provides tunable delay, but it is band limited
- Trade-off between maximum delay and delay bandwidth
- Solution → cascade more than one ORRs

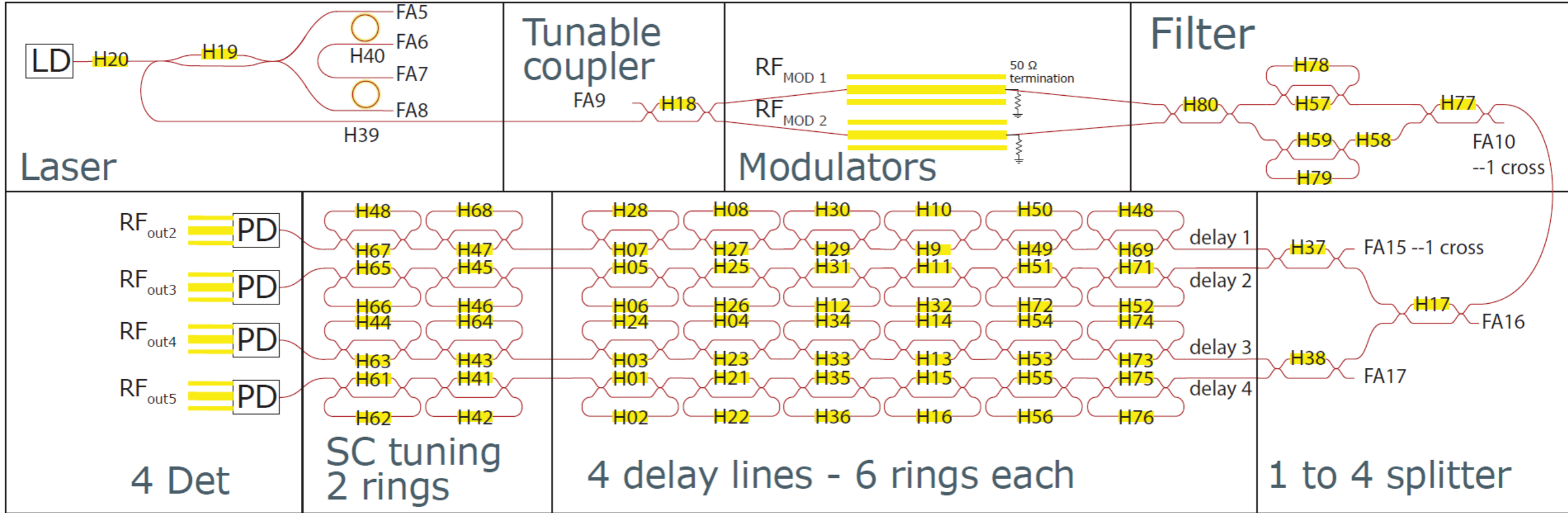


- More ORRs cascaded → more bandwidth but more ripple
- Trade-off between bandwidth, the number of ORR and the delay ripple

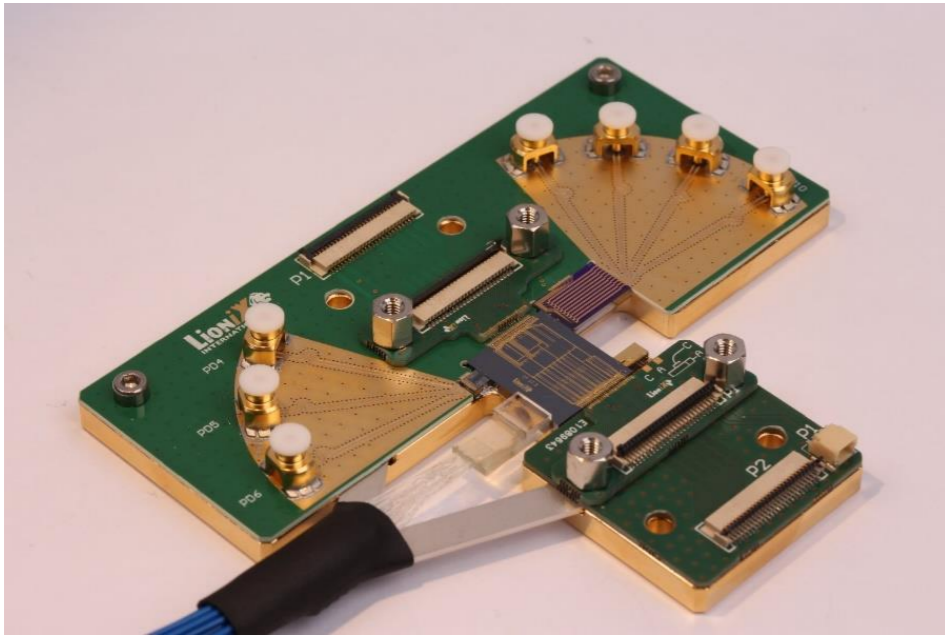
Next step: to arrange the combiners and the ORRs to make a beamformer



1xN Optical Beamforming Network



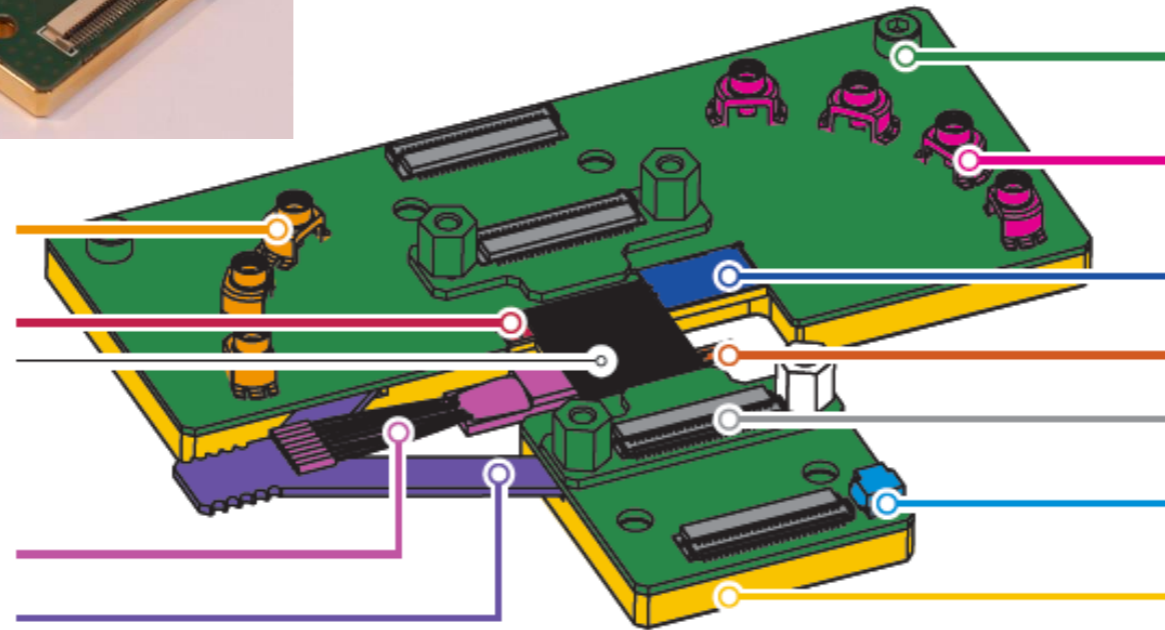
iMWP Hybrid InP-TriPleX Assembly



RF: photodiode connectors

InP photodiodes
TriPleX OBFN

Fiber Array
Fiber strain relief



PCB

RF: modulator connectors

InP modulators

InP gain section

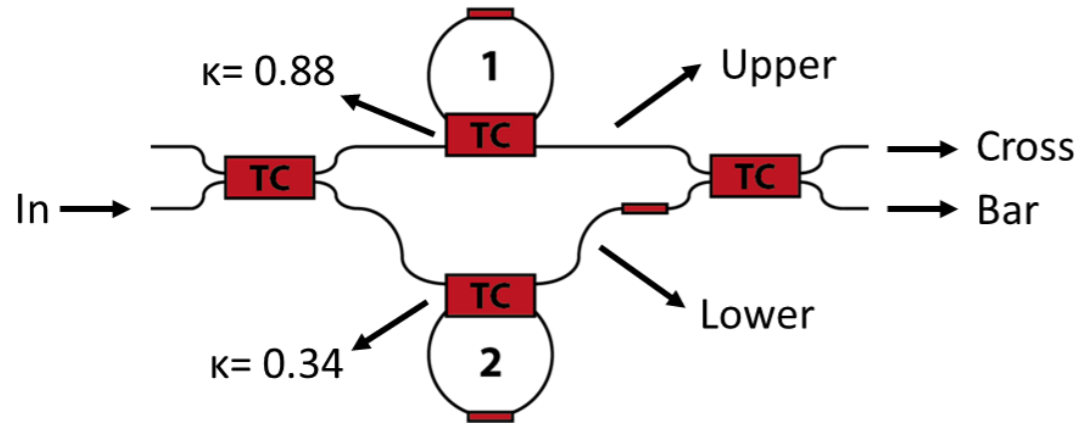
FCC connectors for DC heater drivers

Gain section current connector

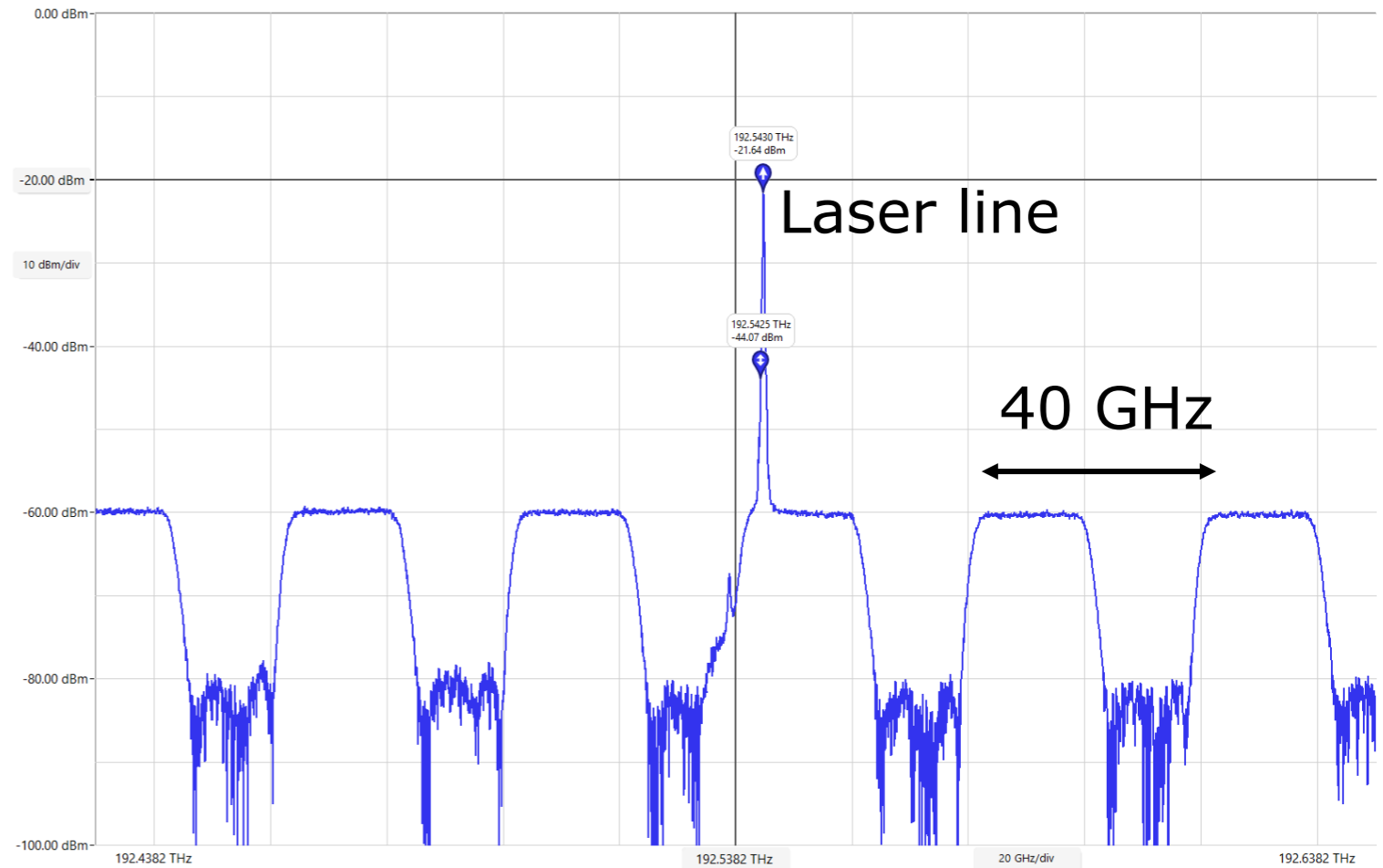
Heat sink

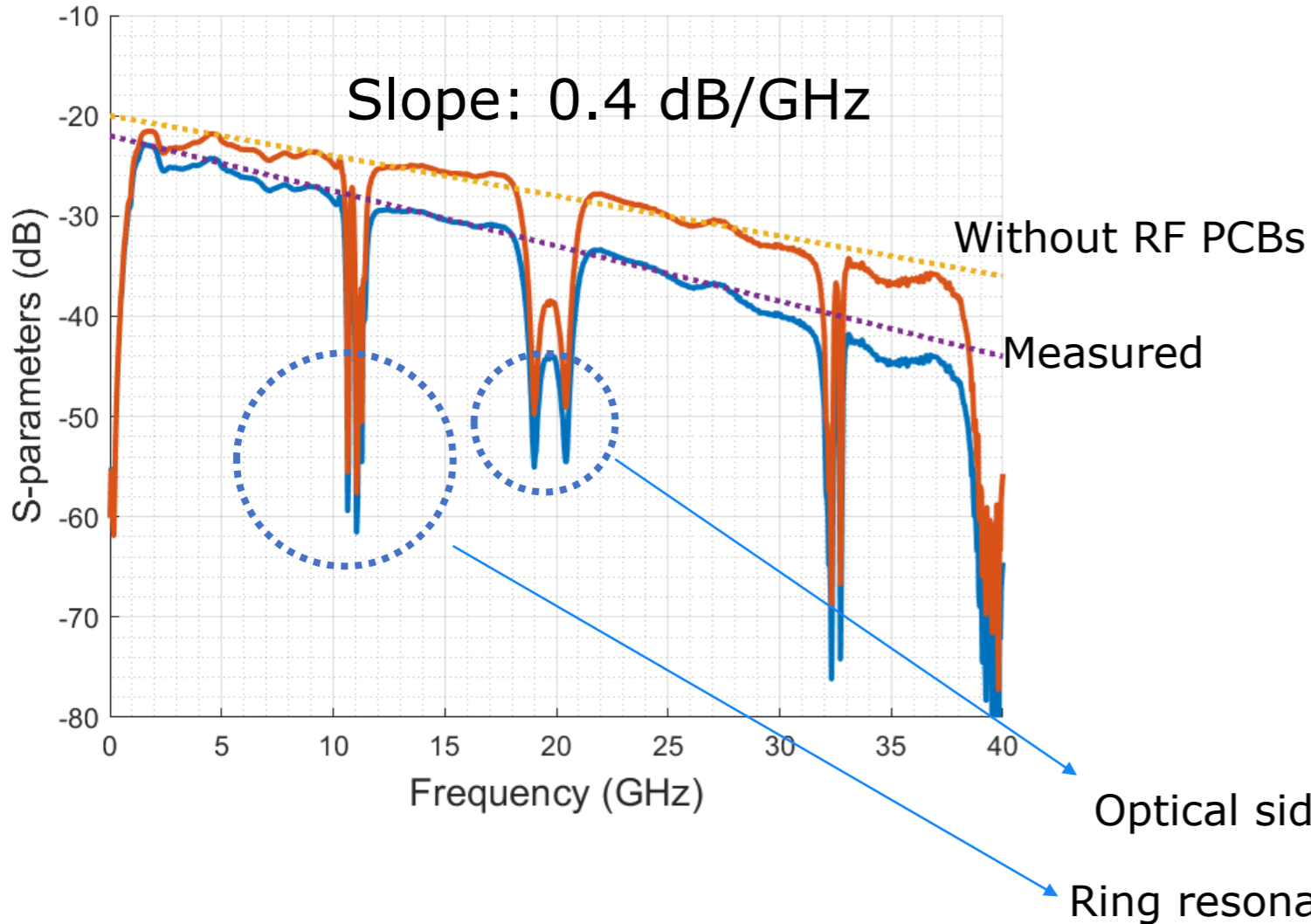


TriPleX- Filter for SSBFC Processing



- Flat filter response
- Passband loss < 0.2 dB
- > 20 dB stopband rejection
- Carrier in the passband
- USB in the passband
- LSB in the stopband





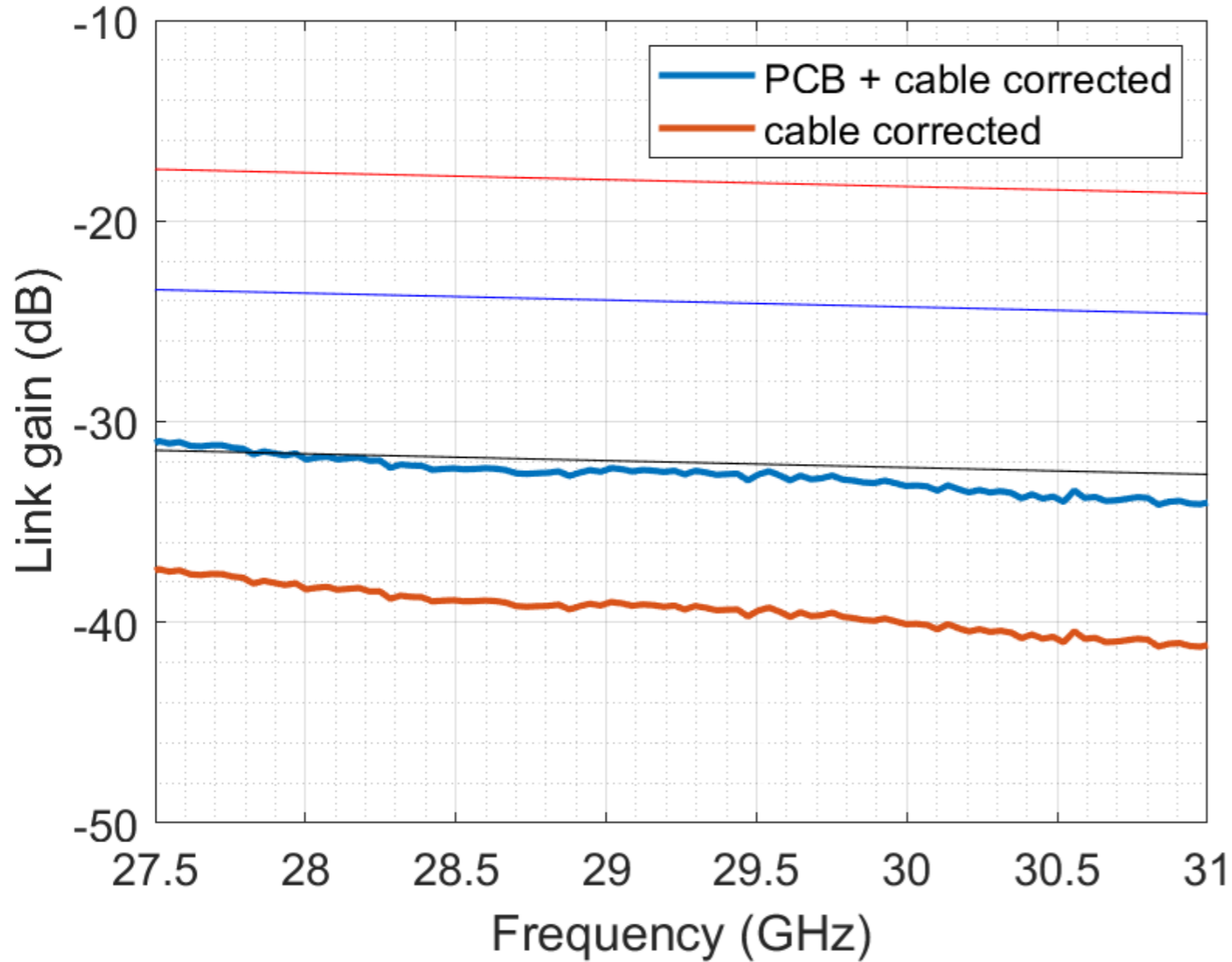
$$I_{PD_DC} = 3.8 \text{ mA}$$

	Freq (GHz)	G (dB)	V_{π} (V)
Measured	5	-22	4.0
	10	-24	4.7
	20	-28	7.7
	30	-32	11.8
Expected	30	-20	3
	20	-17.7	2.3

Reduced link gain is a cause by modulator saturation and detector saturation

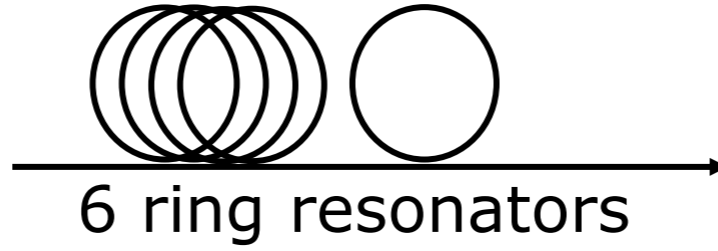


Amplitude Uniformity at 29 GHz

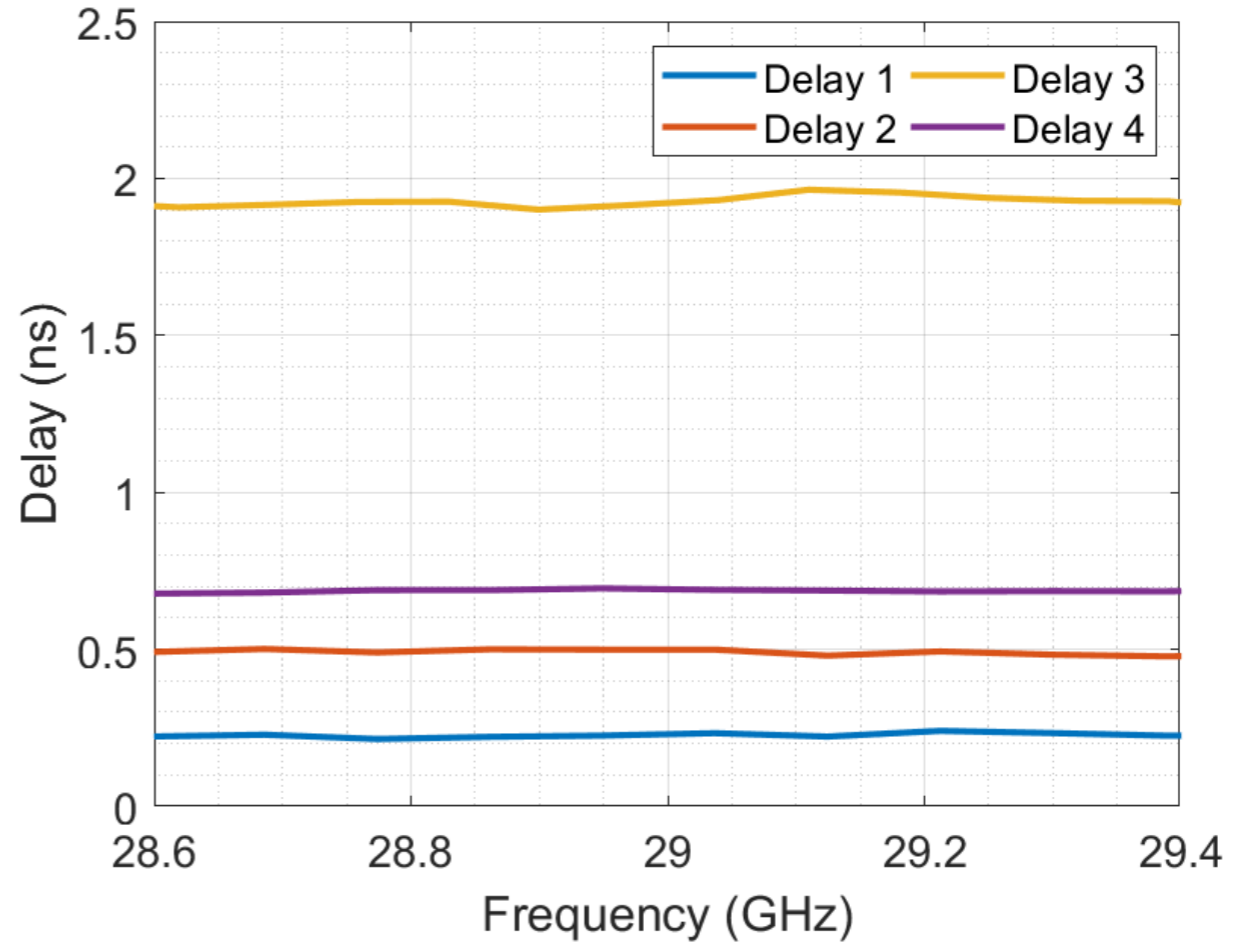
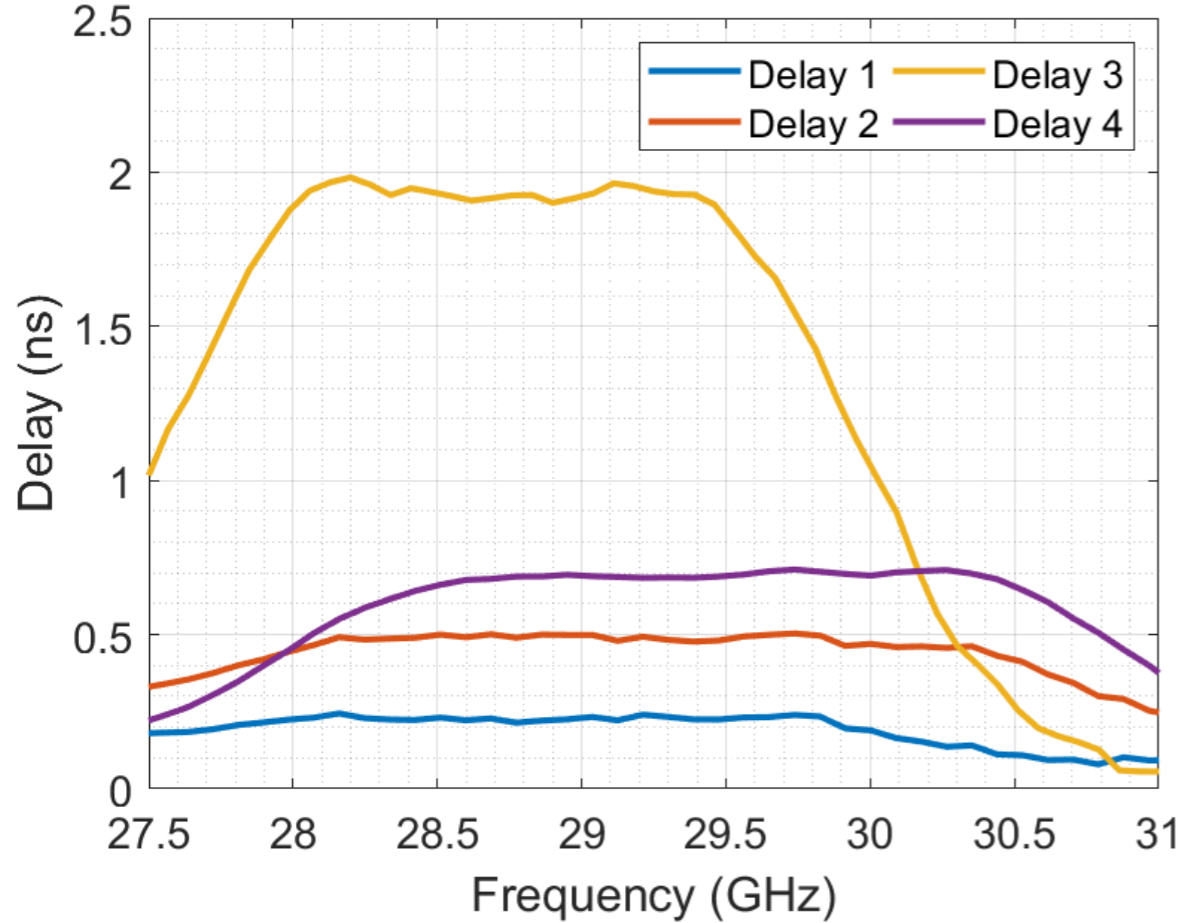


< 1.8 dB over 3.5 GHz
(PCBs + PM + DET)





Tunable Delays



Tunable delay: 0 – 2 ns (= 60 cm)

Variation < 20 ps in 800 MHz



iMWP a Disruption in RF Technology !!

- **Vision:** Towards iMWP (10-300 GHz, Phase Shifting, True Time Delay, Multi-beam, Combining, Splitting, Filtering, RF-in, RF-out)
- RF-Photonic integration is imperative to yield a reliable beamformer
 - **TriPleX™ Si₃N₄/SiO₂** waveguide technology enables low loss, compact, stable, mass producible MWP signal processors
 - InP enables integration of **detectors**, light sources, **narrow-band lasers** and **high-speed modulators**
- **Next step:** High optical power modulators with in-line optical amplification (with SOA)



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